

TLE9844-2QX

Microcontroller with LIN and Power Switches for Automotive Applications

Data Sheet

Rev. 1.0, 2016-05-06

Automotive Power



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Microcontroller with LIN and Power Switches for Automotive Applications

TLE9844-2QX



1 Overview

Summary of Features

- 32-bit ARM Cortex-M0 Core
 - up to 40 MHz clock frequency
 - one clock per machine cycle architecture
 - single cycle multiplier
- On-chip memory
 - 64 KB Flash (including EEPROM)
 - 4 KB EEPROM (emulated in Flash)
 - 768 bytes 100 Time Programmable Memory (100TP)
 - 4 KB RAM
 - Boot ROM for startup firmware and Flash routines
- On-chip OSC
- 2 Low-Side Switches incl. PWM functionality, can be used e.g. as relay driver
- 2 High-Side Switches with cyclic sense option and PWM functionality, e.g. for supplying LEDs or switch panels (min. 150 mA)
- 5 High Voltage Monitor Input pins for wake-up and with cyclic sense with analog measurement option
- 10 General-purpose I/O Ports (GPIO)
- 6 Analog input Ports
- 10-Bit A/D Converter with 6 analog inputs + VBAT_SENSE + VS + 5 high voltage monitoring inputs
- 8-Bit A/D Converter with 7 inputs for voltage and temperature supervision
- Measurement unit with 12 channels together with the onboard 10-Bit A/D converter and data post processing
- 16-Bit timers GPT12, Timer 2 and Timer 21
- Capture/compare unit for PWM signal generation (CCU6)
- 2 full duplex serial interfaces (UART1, UART2), UART1 with LIN support
- 2 synchronous serial channels (SSC1, SSC2)
- On-chip debug support via 2-wire SWD
- LIN Bootstrap loader to program the Flash via LIN (LIN BSL)
- 1 LIN 2.2 transceiver
- Single power supply from 3.0 V to 28 V
- Low-dropout voltage regulators (LDO)
- 5 V voltage supply VDDEXT for external loads (e.g. Hall-sensor)
- Core logic supply at 1.5 V
- Programmable window watchdog (WDT1) with independent on-chip clock source
- Power saving modes:
 - Micro Controller Unit slow-down mode

Туре	Package	Marking
TLE9844-2QX	VQFN-48-31	TLE9844-2QX



VQFN-48-31



Overview

- Sleep Mode with cyclic sense option
- Cyclic wake-up during Sleep Mode
- Stop Mode with cyclic sense option
- · Power-on and undervoltage/brownout reset generator
- Overtemperature protection
- Short circuit protection for all voltage regulators and actuators (High Side, Low Side)
- · Loss of clock detection with fail safe mode for power switches
- Temperature Range T_J: -40 °C up to 150 °C
- Package VQFN-48-31 with LTI feature
- Green package (RoHS compliant)
- AEC Qualified



Overview

1.1 Abbreviations

The following acronyms and terms are used within this document. List see in Table 1.

Table 1 Acronyms				
Acronyms	Name			
AHB	ARM Advanced High-Performance Bus			
CCU6	Capture Compare Unit 6			
CGU	Clock Generation Unit			
CLKMU	Clock Management Unit			
СМИ	Cyclic Management Unit			
DPP	Data Post Processing			
ECC	Error Correction Code			
EEPROM	Electrically Erasable Programmable Read Only Memory			
GPIO	General Purpose Input Output			
HV	High Voltage			
ICU	Interrupt Control Unit			
LDO	Low DropOut voltage regulator			
LIN	Local Interconnect Network			
LSB	Least Significant Bit			
LTI	Lead Tip Inspection			
LV	Low Voltage			
MCU	Microcontroller Unit			
MF	Measurement Functions			
MPU	Memory Protection Unit			
MRST	Master Receive / Slave Transmit, corresponds to MISO in SPI			
MSB	Most Significant Bit			
MTSR	Master Transmit / Slave Receive, corresponds to MOSI in SPI			
MU	Measurement Unit			
NMI	Non Maskable Interrupt			
NVIC	Nested Vector Interrupt Controller			
OSC	Oscillator			
OTP	One Time Programmable			
PBA Peripheral Bridge				
PC	Program Counter			
PCU	Power Control Unit			
PD Pull Down				
PGU Power supply Generation Unit				
PLL	Phase Locked Loop			
PMU	Power Management Unit			
PPB Private Peripheral Bus				

TLE9844-2QX



Overview

Table 1	Acronyms	
Acronyms		Name
PSW		Program Status Word
PU		Pull Up
PWM		Pulse Width Modulation
RAM		Random Access Memory
RCU		Reset Control Unit
rfu		reserved for future use
RMU		Reset Management Unit
ROM		Read Only Memory
SCU		System Control Unit
SOW		Short Open Window (for WDT1)
SPI		Serial Peripheral Interface
SSC		Synchronous Serial Channel
SWD		ARM Serial Wire Debug
TCCR		Temperature Compensation Control Register
TMS		Test Mode Select
TSD		Thermal Shut Down
UART		Universal Asynchronous Receiver Transmitter
VBG		Voltage reference Band Gap
VCO		Voltage Controlled Oscillator
WDT1		Watchdog timer in SCU-PM (System Control Unit - Power Modules)
WMU		Wake-up Management Unit
100TP		100 Times Programmable



Block Diagram

2 Block Diagram









3 Device Pinout and Pin Configuration

3.1 Device Pinout



Figure 2 Device Pinout, TLE9844-2QX



3.2 Pin Configuration

After reset, all pins are configured as input (except supply and LIN pins) with one of the following settings:

- Pull-up enabled only (PU)
- Pull-down enabled only (PD)
- Input with both pull-up and pull-down disabled (I)
- Output with output stage deactivated = high impedance state (Hi-Z)

The functions and default states of the TLE9844-2QX external pins are provided in the following table.

Type: indicates the pin type.

- I/O: Input or output
- I: Input only
- O: Output only
- P: Power supply

Not all alternate functions listed, see Chapter 14.

Symbol	Pin Number	Туре	Reset State	Function	
P0				Alternate fur	6-Bit bidirectional general purpose I/O port. Inctions can be assigned and are listed in the Port Main function is listed below.
P0.0	20	I/O	I/PU	SWD_CLK GPIO	Serial Wire Debug Clock General Purpose IO Alternate function mapping see Table 8
P0.1	17	I/O	I/PU	GPIO	General Purpose IO Alternate function mapping see Table 8
P0.2	22	I/O	I/PD	GPIO	General Purpose IO Alternate function mapping see Table 8
P0.3	23	I/O	I/PU	GPIO	General Purpose IO Alternate function mapping see Table 8
P0.4	24	I/O	I/PU	GPIO	General Purpose IO Alternate function mapping see Table 8
P0.5	25	I/O	I/PU	GPIO	General Purpose IO Alternate function mapping see Table 8
P1				Alternate fur	4-Bit bidirectional general purpose I/O port. actions can be assigned and are listed in the Port Main function is listed below.
P1.0	14	I/O	I	GPIO	General Purpose IO Alternate function mapping see Table 9
P1.1	15	I/O	I	GPIO	General Purpose IO Alternate function mapping see Table 9
P1.2	16	I/O	I	GPIO	General Purpose IO Alternate function mapping see Table 9
P1.4	26	I/O	I	GPIO	General Purpose IO Alternate function mapping see Table 9

Table 2 Pin Definitions and Functions



Symbol	Pin Number	Туре	Reset State	Function	
P2		Port 2 Port 2 is an 8-Bit general purpose input-only port. Alternate functions can be assigned and are listed in the Port description. Main function is listed below.			
P2.0	39	I	I	AN0	ADC1 analog input channel 12 Alternate function mapping see Table 10
P2.1	37	I	I	AN1	ADC1 analog input channel 7 Alternate function mapping see Table 10
P2.2	33	I	Ι	AN2	ADC1 analog input channel 8 Alternate function mapping see Table 10
P2.3	36	I	I	AN3	ADC1 analog input channel 9 Alternate function mapping see Table 10
P2.4	32	I	I	XTAL1 ¹⁾	Alternate function mapping see Table 10 External oscillator input
P2.5	31	l O	l Hi-Z	XTAL2 ¹⁾	Alternate function mapping see Table 10 External oscillator output
P2.6	34	I	I	AN6	ADC1 analog input channel 10 Alternate function mapping see Table 10
P2.7	35	I	I	AN7	ADC1 analog input channel 11 Alternate function mapping see Table 10
Power Supp	oly				
VS	47	Ρ	_	Battery sup	pply input
VDDP	44	Р	-		oply (5.0 V). Do not connect external loads. For bypass capacitors.
VDDC	42	Р	-	Core supply (1.5 V during Active Mode, 0.9 V during Stop Mode). Do not connect external loads. For buffer/bypass capacitor.	
VDDEXT	45	Р	_	External vo	ltage supply output (5.0 V, 20 mA)
GNDLS	13	Р	_		round LS1, LS2
GNDP	19, 30	Р	_	Core suppl	y ground
GNDA	43	Р	_	Analog sup	pply ground
GNDLIN	2	Р	_	LIN ground	
Monitor Inp	uts				
MON1	5	1	1	High Volta	ge Monitor Input 1
MON2	6	I	1	High Volta	ge Monitor Input 2
MON3	7	1	1	High Volta	ge Monitor Input 3
MON4	8	I	1	High Volta	ge Monitor Input 4
MON5	9	I	1	High Volta	ge Monitor Input 5
High-Side S	witch / Low-Side	Switch	n Outputs	6	
LS1	11	0	Hi-Z	Low-Side s	witch output 1

Table 2 Pin Definitions and Functions (cont'd)



Symbol	Pin Number	Туре	Reset State	Function	
LS2	12	0	Hi-Z	Low-Side Switch output 2	
HS1	3	0	Hi-Z	High-Side Switch output 1	
HS2	4	0	Hi-Z	High-Side Switch output 2	
LIN Interface					
LIN	1	I/O	PU	LIN bus interface input/output	
Others					
TMS	18	I	I/PD	TMStest mode select inputSWD_IOSerial Wire Debug input/output	
RESET	21	I/O	I/O/PU	Reset input/output, not available during Sleep Mode	
VBAT_SENSE	48	I	I	Battery supply voltage sense input	
N.C.	10, 27, 28, 29, 38, 40, 41, 46	-	-	Not connected, can be connected to GND	
EP	_	_	_	Exposed Pad, connect to GND	

1) configurable by user



Modes of Operation

4 Modes of Operation

This highly integrated circuit contains analog and digital functional blocks. For system and interface control an embedded 32-Bit Cortex-M0 microcontroller is included. For internal and external power supply purposes, on-chip low drop-out regulators are existent. An internal oscillator (no external components necessary) provides a cost effective and suitable clock in particular for LIN slave nodes. As communication interface, a LIN transceiver and several High Voltage Monitor Inputs with adjustable threshold and filters are available. Furthermore two High-Sides Switches (e.g. for driving LEDs or powering of switches), two low-side switches (e.g. for relays) and several general purpose input/outputs (GPIO) with pulse-width modulation (PWM) capabilities are available.

The Micro Controller Unit supervision and system protection including reset feature is controlled by a programmable window watchdog. A cyclic wake-up circuit, supply voltage supervision and integrated temperature sensors are available on-chip.

All relevant modules offer power saving modes in order to support terminal 30 connected automotive applications. A wake-up from the power saving mode is possible via a LIN bus message, via the monitoring inputs or repetitive with a programmable time period (cyclic wake-up).

The integrated circuit is available in a package with 0.5 mm pitch and is designed to withstand the challenging conditions of automotive applications.

The TLE9844-2QX has several operational modes mainly to support low power consumption requirements. The low power modes and state transitions are depicted in **Figure 3** below.



Figure 3 Power Control State Diagram



Modes of Operation

Reset Mode

The Reset Mode is a transition mode e.g. during power-up of the device after a power-on reset. In this mode the on-chip power supplies are enabled and all other modules are initialized. Once the core supply VDDC is stable, the Active Mode is entered. In case the watchdog timer WDT1 fails for more than four times, a fail-safe transition to the Sleep Mode is done.

Active Mode

In Active Mode all modules are activated and the TLE9844-2QX is fully operational.

Stop Mode

The Stop Mode is one out of two major low power modes. The transition to the low power modes is done by setting the respective Bits in the mode control register. In Stop Mode the embedded microcontroller is still powered allowing faster wake-up reaction times, but not clocked. A wake-up from this mode is possible by LIN bus activity, the High Voltage Monitor Input pins or the respective 5V GPIOs.

Sleep Mode

The Sleep Mode is a major low-power mode. The transition to the low-power modes is done by setting the respective Bits in the Micro Controller Unit mode control register. The sleep time is configurable. In Sleep Mode the embedded microcontroller power supply is deactivated, allowing the lowest system power consumption, but the wake-up time is longer compared to the Stop Mode. In this mode a 64 bit wide buffer for data storage is available. A wake-up from this mode is possible by LIN bus activity or the High Voltage Monitor Input pins and cyclic wake. A wake-up from Sleep Mode behaves similar to a power-on reset. While changing into Sleep Mode, no incoming wake-requests are lost (i.e. no dead-time). It is possible to enter sleep-mode even with LIN dominant.

Cyclic Wake-up Mode

The cyclic wake-up mode is a special operating mode of the Sleep Mode and the Stop Mode. The transition to the cyclic wake-up mode is done by first setting the respective Bits in the mode control register followed by the SLEEP or STOP command. Additional to the cyclic wake-up behavior (wake-up after a programmable time period), the wake-up sources of the normal Stop Mode and Sleep Mode are available.

Cyclic Sense Mode

The cyclic sense mode is a special operating mode of the Sleep Mode and the Stop Mode. The transition to the cyclic sense mode is done by first setting the respective Bits in the mode control register followed by the STOP or SLEEP command. In cyclic sense mode the High-Side Switch can be switched on periodically for biasing some switches for example. The wake-up condition is configurable, when the sense result of defined monitor inputs at a window of interest changed compared to the previous wake-up period or reached a defined state respectively. In this case the Active Mode is entered immediately.

The following table shows the possible power mode configurations of each major module or function respectively.

Module/function	Active Mode	Sleep Mode	Stop Mode	Comment				
VPRE, VDDP, VDDC	ON	OFF	ON	-				
VDDEXT	ON/OFF	OFF	cyclic ON/OFF	-				
HSx	ON/OFF	cyclic ON/OFF	cyclic ON/OFF	cyclic sense				
LSx	ON/OFF	OFF	OFF	_				
LIN TRx	ON/OFF	wake-up only / OFF	wake-up only/ OFF	-				

Table 3	Power Mode	Configurations
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Modes of Operation

Module/function	Active Mode	Sleep Mode	Stop Mode	Comment
MONx (wake-up)	n.a.	disabled/static/ cyclic	disabled/static/ cyclic	cyclic: combined with HS=on
MONx (measurement)	ON/OFF	OFF	OFF	available on all channels
VS sense	ON/OFF brownout detection	brownout detection	brownout detection	brownout det. done in PCU
VBAT_SENSE	ON/OFF	OFF	OFF	-
GPIO 5V	ON	OFF	ON	-
WDT1	ON	OFF	OFF	-
CYCLIC WAKE	n.a.	cyclic wake-up/ cyclic sense/OFF	cyclic wake-up/ cyclic sense/OFF	cyclic sense with HS; wake-up needs MC for enter Sleep Mode again
Measurement	ON ¹⁾	OFF	OFF	-
Micro Controller Unit	ON/slow- down/STOP	OFF	OFF	-
CLOCK GEN (MC)	ON	OFF	OFF	-
LP_CLK (f _{LP_CLK})	ON	OFF	OFF	WDT1
$LP_CLK2 (f_{LP_CLK2})$	ON	ON	ON	for cyclic wake-up

Table 3 Power Mode Configurations (cont'd)

1) May not be switched off due to safety reasons

Wake-up Source Prioritization

All wake-up sources have the same priority. In order to handle the asynchronous nature of the wake-up sources, the first wake-up signal will initiate the wake-up sequence. Nevertheless all wake-up sources are latched in order to provide all wake-up events to the application software. The software can clear the wake-up source flags. It is ensured, that no wake-up event is lost.

As default wake-up sources, MON inputs and cyclic wake are activated after power-on reset, LIN is disabled as wake-up source by default.

Wake-up Levels and Transitions

The wake-up can be triggered by rising, falling or both signal edges for each monitor input individually.



5 Power Management Unit (PMU)

5.1 Features

- System modes control (startup, sleep, stop and active)
- Power management (cyclic wake)
- Control of system voltage regulators with diagnosis (overload, short, overvoltage)
- Fail safe mode detection and operation in case of system errors (watchdog fail)
- Wake-up sources configuration and management (LIN, MON, GPIOs)
- System error logging

5.2 Introduction

The purpose of the power management unit is to ensure the fail safe behavior of the system IC. Therefore the power management unit controls all system modes including the corresponding transitions. The power management unit is responsible for generating all needed voltage supplies for the embedded MCU (VDDC, VDDP) and the external supply (VDDEXT). Additionally, the PMU provides well defined sequences for the system mode transitions and generates hierarchical reset priorities. The reset priorities control the reset behavior of all system functionalities especially the reset behavior of the embedded MCU. All these functions are controlled by finite state machines. The system master functionality of the PMU requires the generation of an independent logic supply and system clock. Therefore the PMU has a module internal logic supply and system clock which works independently of the MCU clock.



5.2.1 Block Diagram

The following figure shows the structure of the Power Management Unit. **Table 4** describes the submodules more detailed.



Figure 4 Power Management Unit Block Diagram

Table 4 Description of PMU Submodules

Mod. Name	Modules	Functions
Power Down Supply	Independent Supply Voltage Generation for PMU	This supply is dedicated to the PMU to ensure an independent operation from generated power supplies (VDDP, VDDC).
$\overline{LP_CLK}$ $(=f_{LP_CLK})$	 Clock Source for all PMU submodules Backup Clock Source for System Clock Source for WDT1 	This ultra low power oscillator generates the clock for the PMU. This clock is also used as backup clock for the system in case of PLL Clock failure and as independent clock source for WDT1.
$\frac{\text{LP}_{\text{CLK2}}}{(= f_{\text{LP}_{\text{CLK2}}})}$	Clock Source for PMU	This ultra low power oscillator generates the clock for the PMU in Stop Mode and in the cyclic modes.
Peripherals	Peripheral Blocks of PMU	These blocks include the analog peripherals to ensure a stable and fail safe PMU startup and operation (bandgap, bias).



Mod. Name	Modules	Functions
Power Supply Generation Unit (PGU)	Voltage regulators for VDDP and VDDC	This block includes the voltage regulators for the pad supply (VDDP) and the core supply (VDDC).
VDDEXT	Voltage regulator for VDDEXT to supply external modules (e.g. Sensors)	This voltage regulator is a dedicated supply for external modules.
PMU-SFR	All PMU relevant Extended Special Function Registers	This module contains all PMU relevant registers, which are needed to control and monitor the PMU.
PMU-PCU	Power Control Unit of the PMU	This block is responsible for controlling all power related actions within the PGU Module.It also contains all regulator related diagnosis like under- and overvoltage detection, overcurrent and short circuit diagnoses.
PMU-WMU	Wake-up Management Unit of the PMU	This block is responsible for controlling all Wake-up related actions within the PMU Module.
PMU-CMU	Cyclic Management Unit of the PMU	This block is responsible for controlling all actions within cyclic mode.
PMU-RMU	Reset Management Unit of the PMU	This block generates resets triggered by the PMU like undervoltage or short circuit reset, and passes all resets to the relevant modules and their register. A reset status register with every reset source is available.

Table 4 Description of PMU Submodules (cont'd)



5.2.2 PMU Modes Overview

The following state diagram shows the available modes of the device.





5.3 Power Supply Generation (PGU)

5.3.1 Voltage Regulator 5.0V (VDDP)

This module represents the 5 V voltage regulator, which provides the pad supply for the parallel port pins and other 5 V analog functions (e.g. LIN Transceiver).

Features

- 5 V low-drop voltage regulator
- Overcurrent monitoring and shutdown with MCU signalling (Interrupt)
- Overvoltage monitoring with MCU signalling (Interrupt)
- Undervoltage monitoring with MCU signalling (Interrupt)
- Undervoltage monitoring with Reset (Undervoltage Reset, V_{DDPUV})
- Overtemperature shutdown with MCU signalling (Interrupt)
- Pre-Regulator for VDDC Regulator
- GPIO Supply
- Pull Down Current Source at the output for Sleep Mode only (typ.5 mA)

The output capacitor $C_{\rm VDDP}$ is mandatory to ensure a proper regulator functionality.



Figure 6 Module Block Diagram of VDDP Voltage Regulator



5.3.2 Voltage Regulator 1.5V (VDDC)

This module represents the 1.5 V voltage regulator, which provides the supply for the microcontroller core, digital peripherals and other chip internal analog 1.5 V functions (e.g. ADC).

Features

- 1.5 V low-drop voltage regulator
- Overcurrent monitoring and Shutdown with MCU signalling (Interrupt)
- Overvoltage monitoring with MCU signalling (Interrupt)
- Undervoltage monitoring with MCU signalling (interrupt)
- Undervoltage monitoring with reset
- Overtemperature Shutdown with MCU signalling (Interrupt)
- Pull Down Current Source at the output for Sleep Mode only (typ. 100 $\mu A)$

The output capacitor $C_{\rm VDDC}$ is mandatory to ensure a proper regulator functionality.



Figure 7 Module Block Diagram of VDDC Voltage Regulator



5.3.3 External Voltage Regulator 5.0V (VDDEXT)

This module represents the 5 V voltage regulator, which serves as a supply for external circuits. It can be used e.g. to supply an external sensor, LEDs or potentiometers.

Features

- Switchable (by software) +5 V, low-drop voltage regulator
- Switch-on undervoltage blanking time in order to drive small capacitive loads
- Intrinsic current limitation
- Undervoltage monitoring and shutdown with MCU signalling (Interrupt)
- Overtemperature Shutdown with MCU signalling (Interrupt)
- Pull Down Current Source at the output for Sleep Mode only (typ. 100 μA)
- Cyclic sense option together with GPIOs
- Low current mode available to ensure reduced stop mode current consumption. In this mode current capability
 is reduced to I_{VDDEXT_LCM}

The output capacitor C_{VDDEXT} is mandatory to ensure a proper regulator functionality.



Figure 8 Module Block Diagram



5.3.4 Power-on Reset Concept



Figure 9 Power-on Reset Concept



6 System Control Unit - Digital Modules (SCU-DM)

6.1 Features

- Flexible clock configuration features
- Reset management of all system resets
- System modes control for all power modes (active, power down, sleep)
- · Interrupt enabling for many system peripherals
- General purpose input output control
- Debug mode control of system peripherals

6.2 Introduction

The System Control Unit (SCU) supports all central control tasks in the TLE9844-2QX. The SCU is made up of the following sub-modules:

- Clock System and Control (CGU)
- Reset Control (RCU)
- Power Management (PCU)
- Interrupt Management (ICU)
- General Port Control
- Flexible Peripheral Management
- Module Suspend Control
- Error Detection and Correction in Data Memory
- Miscellaneous Control
- Register Mapping



TLE9844-2QX

System Control Unit - Digital Modules (SCU-DM)

6.2.1 Block Diagram



Figure 10 System Control Unit - Digital Modules Block Diagram

IO description of SCU_DM:

- CGU:
 - $-f_{sys}$; system clock
 - LP_CLK; low-power backup clock
- RCU:
 - 1V5DidPOR; Undervoltage reset of power down supply
 - PMU_PIN; Reset generated by reset pin
 - PMU_ExtWDT; WDT1 reset
 - PMU_SOFT; Software reset
 - PMU_Wake; Stop Mode exit with reset
 - Reset_Type_3; Peripheral reset (contains all resets)



- Reset_Type_4; Peripheral reset (without SOFT)
- Baudrate generator:
 - f_{BR}; Baudrate clock for UART
- Port Control:
 - P0_POCONy.PDMx; driver strength control
 - P1_POCONy.PDMx; driver strength control
- MISC:
 - MODPISELx; Mode selection registers for UART (source selection) and Timer (trigger or count selection)



6.3 Clock Generation Unit

The Clock Generation Unit (CGU) provides a flexible clock generation for TLE9844-2QX. During user program execution the frequency can be programmed for an optimal ratio between performance and power consumption. Therefore the power consumption can be adapted to the actual application state.

The CGU in the TLE9844-2QX consists of one oscillator circuit (OSC_HP), a Phase-Locked Loop (PLL) module including an internal oscillator (OSC_PLL) and a Clock Control Unit (CCU). The CGU can convert a low-frequency input/external clock signal to a high-frequency internal clock.

The system clock f_{SYS} is generated out of the following selectable clocks:

- PLL clock output f_{PLL}
- Direct clock from oscillator OSC_HP f_{OSC}
- Direct output of internal Oscillator f_{INTOSC}
- Low precision clock f_{LP_CLK} (HW-enabled for startup after reset and during power-down wake-up sequence) The following sections describe the different parts of the CGU.

6.3.1 Low Precision Clock

The clock source LP_CLK is a low-precision RC oscillator (LP-OSC, see f_{LP_CLK}) that is enabled by hardware as an independent clock source for the TLE9844-2QX startup after reset and during the power-down wake-up sequence. There is no user configuration possible on f_{LP_CLK} .

6.3.2 High Precision Oscillator Circuit (OSC_HP)

The high precision oscillator circuit, designed to work with both an external crystal oscillator or an external stable clock source, consists of an inverting amplifier with XTAL1 as input, and XTAL2 as output.

Figure 11 shows the recommended external circuitries for both operating modes, External Crystal Mode and External Input Clock Mode.

6.3.2.1 External Input Clock Mode

When supplying the clock signal directly, not using an external crystal and bypassing the oscillator, the input frequency needs to be within the range of 4 MHz to 24 MHz if the PLL VCO part is used.

When using an external clock signal it must be connected to XTAL1. XTAL2 is left open (unconnected).

6.3.2.2 External Crystal Mode

When using an external crystal, its frequency can be within the range of 4 MHz to 6 MHz. An external oscillator load circuitry must be used, connected to both pins, XTAL1 and XTAL2. It consists normally of the two load capacitances C1 and C2, for some crystals a series damping resistor might be necessary. The exact values and related operating range are dependent on the crystal and have to be determined and optimized together with the crystal vendor using the negative resistance method. As starting point for the evaluation, the following load cap values may be used:

Fundamental Mode Crystal Frequency (approx., MHz)	Load Caps C_1, C_2 (pF)
4	33
5	22
6	18

Table 5 External CAP Capacitors





Figure 11 TLE9844-2QX External Circuitry for the OSC_HP



6.3.3 Clock Control Unit

The Clock Control Unit (CCU) receives the clock from the PLL f_{PLL} , the external input clock f_{OSC} , the internal input clock f_{INTOSC} , or the low-precision input clock f_{LP_CLK} . The system frequency is derived from one of these clock sources.



Figure 12 Clock Inputs to Clock Control Unit

The CCU generates all necessary clock signals within the microcontroller from the system clock. It consists of:

- Clock slow down circuitry
- Centralized enable/disable circuit for clock control

In normal running mode, the main module frequencies (synchronous unless otherwise stated) are as follows:

- System frequency, f_{SYS} = up to 40 MHz (measurement interface clock MI_CLK is derived from this clock)
- CPU clock (CCLK, SCLK) = up to 40 MHz (divide-down of NVM access clock)
- NVM access clock (NVMACCCLK) = up to 40 MHz
- Peripheral clock (PCLK, PCLK2, NVMCLK) = up to 40 MHz (equals CPU clock; must be same or higher)

Some peripherals are clocked by PCLK, others clocked by PCLK2 and the NVM is clocked by both NVMCLK and NVMACCCLK. During normal running mode, PCLK = PCLK2 = NVMCLK = CCLK. On wake-up from power-down mode, PCLK2 is restored similarly like NVMCLK, whereas PCLK is restored only after PLL is locked.

For optimized NVM access (read/write) with reduced wait state(s) and with respect to system requirements on CPU operational frequency, bit field NVMCLKFAC is provided for setting the frequency factor between the NVM access clock NVMACCCLK and the CPU clock CCLK.

For the slow down mode, the operating frequency is reduced using the slow down circuitry with clock divider setting at the bit field CLKREL. Bit field CLKREL is only effective when slow down mode is enabled via SFR bit PMCON0.SD bit. Note that the slow down setting of bit field CLKREL correspondingly reduces the NVMACCCLK clock. Slow down setting does not influence the erase and write cycles for the NVM.

Peripherals UART1, UART2, T2 and T21 and are not influenced by CLKREL and either not by NVMCLKFAC, to allow functional LIN communication in slow down mode.

TLE9844-2QX



System Control Unit - Digital Modules (SCU-DM)



Figure 13 Clock Generation from f_{sys} ; CLKOUT Generation



System Control Unit - Power Modules (SCU-PM)

7 System Control Unit - Power Modules (SCU-PM)

7.1 Description of the Power Modules System Control Unit

The System Control Unit of the power modules consists of the following sub-modules:

- Clock Watchdog Unit (CWU): supervision of all power modules relevant clocks with NMI signalling.
- Interrupt Control Unit (ICU): all system relevant interrupt flags and status flags.
- Power Control Unit (PCU): takes over control when device enters and exits Sleep and Stop Mode.
- External Watchdog (WDT1): independent system watchdog to monitor system activity

7.2 Introduction

7.2.1 Block Diagram

The System Control Unit of the power modules consists of the sub-modules in the figure shown below:



Figure 14 Block diagram of System Control Unit - Power Modules

IO description of SCU_PM:

CWU (Clock Watchdog Unit)

- check of f_{svs} = system frequency: output of PLL
- check of MI_CLK = measurement interface clock (analog clock): derived out of f_{sys} by division factors 1/2/3/4
- check of TFILT_CLK = clock used for digital filters: derived out of f_{sys} by configurable division factors



System Control Unit - Power Modules (SCU-PM)

ICU (Interrupt Control Unit)

- PREWARN_SUP_NMI = generation of Prewarn-Supply NMI
- PREWARN_CLK_INT = generation of Prewarn-Clock Watchdog NMI
- INT = generation of MISC interrupts



ARM Cortex-M0 Core

8 ARM Cortex-M0 Core

8.1 Features

The key features of the Cortex-M0 implemented are listed below.

Processor Core. A low gate count core, with low latency interrupt processing:

- Thumb[®] + Thumb-2[®] Instruction Set
- Banked stack pointer (SP) only
- · Handler and thread modes
- Thumb and debug states
- Interruptible-continued instructions LDM/STM, Push/Pop for low interrupt latency
- · Automatic processor state saving and restoration for low latency Interrupt Service Routine (ISR) entry and exit
- ARM architecture v6-M Style
- ARMv6 unaligned accesses
- Systick (typ. 1ms)

Nested Vectored Interrupt Controller (NVIC) closely integrated with the processor core to achieve low latency interrupt processing:

- External interrupts, configurable from 1 to 24
- 7 interrupt priority registers for levels from 0 up to 192 in steps of 64
- Dynamic repriorization of interrupts
- Priority grouping. This enables selection of pre-empting interrupt levels and non pre-empting interrupt levels
- Support for tail-chaining and late arrival of interrupts. This enables back-to-back interrupt processing without the overhead of state saving and restoration between interrupts.
- Processor state automatically saved on interrupt entry, and restored on interrupt exit, with no instruction
 overhead

Bus interfaces

• Advanced High-performance Bus-Lite (AHB-Lite) interfaces



ARM Cortex-M0 Core

8.2 Introduction

The ARM Cortex-M0 processor is a leading 32-bit processor and provides a high-performance and cost-optimized platform for a broad range of applications including microcontrollers, automotive body systems and industrial control systems. Like the other Cortex-family processors, the Cortex-M0 processor implements the Thumb[®]-2 instruction set architecture. With the optimized feature set the Cortex-M0 delivers 32-bit performance in an application space that is usually associated with 8- and 16-bit microcontrollers.

8.2.1 Block Diagram

Figure 15 shows the functional blocks of the Cortex-M0.



Figure 15 Cortex-M0 Block Diagram


Address Space Organization

9 Address Space Organization

The embedded Cortex-M0 MCU offers the following address space organization:



Figure 16 Original Cortex-M0 Memory Map

The TLE9844-2QX manipulates operands in the following memory spaces:

- 64 KByte of Flash memory in code space
- 24 KB Boot ROM memory in code space (used for boot code and IP storage)
- 4 KB RAM memory in code space and data space (RAM can be read/written as program memory or external data memory)
- Special function registers (SFRs) in peripheral linear address space, up to 0.5 GBytes

The figure below shows the detailed address alignment of TLE9844-2QX:



Address Space Organization





Figure 17 TLE9844-2QX Memory Map



Memory Control Unit

10 Memory Control Unit

10.1 Features

- Provides Memory access to ROM, RAM, NVM, Config Sector through AHB-Lite Interface
- MBIST for RAM
- MBIST for ROM
- NVM Configuration with Special Function Registers through AHB-Lite Interface
- Hardware Memory Protection Logic

10.2 Introduction

10.2.1 Block Diagram

The Memory Control Unit is divided in the following sub-modules:

- NVM Memory module (embedded Flash Memory)
- RAM memory module
- BootROM memory module
- Memory protection Unit (MPU) module



TLE9844-2QX

Memory Control Unit



Figure 18 Memory Control Unit Block View

Functional Features for RAM

- 4 KB RAM
- Error correction code (ECC) for detection of single bit and double bit errors and dynamic correction of single bit errors
- Single byte access



NVM Module (Flash Memory)

11 NVM Module (Flash Memory)

The Flash memory provides an embedded user-programmable non-volatile memory, allowing fast and reliable storage of user code and data.

Features

- In-System Programming via LIN (Flash mode) and SWD
- Error Correction Code (ECC) for detection of single Bit and double Bit errors and dynamic correction of single Bit errors on Data Block (Double words, 64 bits).
- Interrupt and signaling of double bit error by NMI, address of double bit error readable by FW API user routine.
- Possibility of checking single bit error occurrence by ROM routines
- Program width of 128 Byte (page)
- Minimum erase width of 128 Byte (page)
- Integrated hardware support for EEPROM emulation
- 8 Byte read access
- Physical read access time: typ. 75 ns
- · Code read access acceleration integrated; read buffer
- Page program time: typ. 3 ms
- Programming time for 64KB via Debug Interface: < 1800 ms (typ.)
- Page erase (128 bytes) and sector erase (4K bytes) time: typ. 4ms
- 3 separate keys for data area, program area and BSL area
- Password protection for three configurable program flash areas, three separate keys for data, program and BSL
- Security option to protect read out via debug interface in application run mode. NVM protection mode available, which can be enabled/disabled with password
- Write/erase access to 100TP (e.g. option bytes) is possible via the debug interface
- Note: The user has to ensure that no flash operations which change the content of the flash get interrupted at any time.

The clock for the NVM is supplied with the system frequency f_{sys} . Integrated firmware routines are provided to ease NVM, and other operations including EEPROM emulation.

The TLE9844-2QX NVM module provides physical implementation of the memory module as well as needed complementary features and interface towards the core.

The module provides proper access to the memory through 2 AHB-Lite interfaces: a 8-bit data interface for NVM internal register access and a 32-bit data interface for code/data access both multiplexed on Cortex-M0 system bus.

The TLE9844-2QX NVM module consists of the memory cell array and all the control circuits and registers needed to access the array itself. The 64 Kbyte data module is mapped in the Cortex-M0 code address range 1100000H - 1100FFFFH while the dedicated SFRs are mapped in the Cortex-M0 system address range .

Access of NVM module is granted through the AMBA matrix block that forwards to the memory modules AHB-Lite interfaces the requests generated by the masters according to the defined priority policy.



NVM Module (Flash Memory)

11.1 Definitions

This section defines the nomenclature and some abbreviations. The used flash memory is a non-volatile memory ("NVM") based on a floating gate one-transistor cell. It is called "non-volatile" because the memory content is kept when the memory power supply is shut off.

11.1.1 General Definitions

Logical and Physical States

Erasing

The erased state of a cell is '1'. Forcing an NVM cell to this state is called erasing. Erasing is possible with a granularity of a page (see below).

Writing

The written state of a cell is '0'. Forcing an NVM cell to this state is called writing. Each bit can be individually written.

Programming

The combination of erasing and writing is called 'programming'. Programming often means also writing a previously erased page.

The wording 'write' or 'writing' are also used for accessing special function registers and the assembly buffer. The meaning depends therefore on the context.

The above listed processes have certain limitations:

Retention: This is the time during which the data of a flash cell can be read reliably. The retention time is a statistical figure that depends on the operating conditions of the flash array (temperature profile) and the accesses to the flash array. With an increasing number of program/erase cycles (see endurance) the retention is lowered. Drain and gate disturbs decrease data retention as well.

Endurance: As described above, the data retention is reduced with an increasing number of program/erase cycles. A flash cell incurs one cycle whenever its page or sector is erased. This number is called "endurance". As said for the retention, it is a statistical figure that depend on operating conditions and the use of the flash cells and on the required quality level.

Drain Disturb: Because of using a so called "one-transistor" flash cell each program access disturbs all pages of the same sector slightly. Over long these "drain disturbs" make 0 and 1 values indistinguishable and thus provoke read errors. This effect is again interrelated with the retention. A cell that incurred a high number of drain disturbs will have a lower retention. The physical sectors of the flash array are isolated from each other. So pages of a different sector do not incur a drain disturb. this effect must be therefore considered when the page erase feature is used or when re-programming an ready programmed page (implicitly causing an erase of the page before writing the new data).

Data Portions

TLE9844-2QX



NVM Module (Flash Memory)



Figure 19 Logical Structure of the NVM Core

Doubleword

A doubleword consists of 64 bits. A doubleword represents the data size that is read from or written to the NVM core module within one access cycle.

Block

A block consists of one doubleword and its associated ECC data (64 bit data and 8 bit ECC). A block represents the smallest data portion that can be changed in the assembly buffer. Since the ECC protects 64 bits, when a byte is written to the assembly buffer automatically an NVM internal read of the complete block is triggered, the byte and the ECC are updated and the complete block is written back to the assembly buffer.

Mapblock

A map block consists of a module specific number of ECC -protected bits that hold the necessary information to map a physical page to a logical page.

Page

A page consists of 16 blocks and one map block.

Spare Page



NVM Module (Flash Memory)

A spare page is an additional page in a sector used in each programming routine to allow tearing-safe programming.

Sector

A sector consists of 32 logical and 33 physical pages.



Interrupt System

12 Interrupt System

12.1 Features

- Up to 24 interrupt nodes for on-chip peripherals
- Up to 8 NMI nodes for critical system events
- Maximum flexibility for all 24 interrupt nodes

12.2 Introduction

12.2.1 Overview

The TLE9844-2QX supports 24 interrupt vectors with 4 priority levels. 22 of these interrupt vectors are assigned to the on-chip peripherals: GPT12, SSC1, SSC2, CCU6, Low-Side Switch, High-Side Switch and A/D Converter are each assigned to one dedicated interrupt vector; while UART1 and Timer2 or UART2, External Interrupt 2 and Timer21 share interrupt vectors. Two vectors are dedicated for External Interrupt 0 and 1.

Service Request	Node ID	Description	
GPT1	0	GPT1 Interrupt	
GPT2	1	GPT2 Interrupt	
MU	2	MU interrupt / ADC2, VBG interrupt	
ADC1	3	ADC10 Bit interrupt	
CCU0	4	CCU6 node 0 interrupt	
CCU1	5	CCU6 node 1 interrupt	
CCU2	6	CCU6 node 2 interrupt	
CCU3	7	CCU6 node 3 interrupt	
SSC1	8	SSC1 interrupt (receive, transmit, error)	
SSC2	9	SSC2 interrupt (receive, transmit, error)	
UART1	10	UART1 (ASC-LIN) interrupt (receive, transmit), t2, linsync1, LIN	
UART2	11	UART2 interrupt (receive, transmit), t21, External interrupt (EINT2)	
EXINT0	12	External interrupt (EINT0), wakeup	
EXINT1	13	External interrupt (EINT1)	
WAKEUP	14	Wakeup interupt (generated by a wakeup event)	
rfu	15	Reserved for future use	
rfu	16	Reserved for future use	
LS1	17	Low Side 1 Interrupt	
LS2	18	Low Side 2 Interrupt	
HS1	19	High Side 1 Interrupt	
HS2	20	High Side 2 Interrupt	
rfu	21	Reserved for future use	

Table 6Interrupt Vector Table



TLE9844-2QX

Interrupt System

i and o interrupt					
Service Request	Node ID	Description			
MONx	22	MONx Interrupt, wakeup			
Port 2.x	23	Port 2.x - DPP1			

Table 6Interrupt Vector Table (cont'd)

Table 7NMI Interrupt Table

Service Request			
PLL NMI			
NVM Operation Complete NMI	NMI	NVM Operation Complete	
Overtemperature NMI	NMI	System Overtemperature	
Oscillator Watchdog NMI	NMI	Oscillator Watchdog and MI_CLK Watchdog Timer Overflow	
NVM Map Error NMI	NMI	NVM Map Error	
ECC Error NMI	NMI	RAM / NVM Uncorrectable ECC Error	
Supply Prewarning NMI	NMI	Supply Prewarning	



Watchdog Timer (WDT1)

13 Watchdog Timer (WDT1)

13.1 Features

In Active Mode, the WDT1 acts as a windowed watchdog timer, which provides a highly reliable and safe way to recover from software or hardware failures.

The WDT1 is always enabled in Active Mode. In Sleep Mode, Stop Mode and Debug Mode the WDT1 is disabled.

Functional Features

- Watchdog Timer is operating with a from the system clock (f_{SYS}) independent clock source ($f_{LP CLK}$)
- Windowed Watchdog Timer with programmable timing (16, 32, 48, ..., 1008ms period) in Active Mode
- Long open window (200 ms) after power-up, reset, wake-up
- Short open window (30 ms) to facilitate Flash programming
- · System safety shutdown to Sleep Mode after 5 missed WDT1 services
- Watchdog is disabled in Debug Mode
- Watchdog cannot be deactivated in Normal Mode
- Watchdog reset is stored in reset status register



13.2 Introduction

The behavior of the Watchdog Timer in Active Mode is depicted in Figure 20.



Figure 20 Watchdog Timer Behavior



14 GPIO Ports and Peripheral I/O

The TLE9844-2QX has 18 port pins organized into three parallel ports: Port 0 (P0), Port 1 (P1) and Port 2 (P2). Each port pin has a pair of internal pull-up and pull-down devices that can be individually enabled or disabled. P0 and P1 are bidirectional and can be used as general purpose input/output (GPIO) or to perform alternate input/output functions for the on-chip peripherals. When configured as an output, the open drain mode can be selected. On Port 2 (P2) analog inputs are shared with general purpose input.

14.1 Features

- 10 GPIOs (P0.x & P1.x), 6 analog inputs (P2.x) and two additional analog inputs shared with a XTAL feature (P2.4, P2.5).
- Strong pull-up at Reset-pin and Hall-inputs (except P2.x)

Bidirectional Port Features (P0, P1)

- Configurable pin direction
- Configurable pull-up/pull-down devices
- Configurable open drain mode
- Configurable drive strength
- Transfer of data through digital inputs and outputs (general purpose I/O)
- Alternate input/output for on-chip peripherals

Analog Port Features (P2)

- Configurable pull-up/pull-down devices
- Transfer of data through digital inputs
- Alternate inputs for on-chip peripherals

14.2 Introduction



14.2.1 Port 0 and Port 1

Figure 21 shows the block diagram of an TLE9844-2QX bidirectional port pin. Each port pin is equipped with a number of control and data bits, thus enabling very flexible usage of the pin.



Figure 21 General Structure of Bidirectional Port



TLE9844-2QX

GPIO Ports and Peripheral I/O

14.2.2 Port 2

Figure 22 shows the structure of an input-only port pin. Each P2 pin can only function in input mode. Register P2_DIR is provided to enable or disable the input driver. When the input driver is enabled, the actual voltage level present at the port pin is translated into a logic 0 or 1 via a Schmitt-Trigger device and can be read via the register P2_DATA. Each pin can also be programmed to activate an internal weak pull-up or pull-down device. Register P2_PUDSEL selects whether a pull-up or the pull-down device is activated while register P2_PUDEN enables or disables the pull device. The analog input (AnalogIn) bypasses the digital circuitry and Schmitt-Trigger device for direct feed-through to the ADC input channel.



Figure 22 General Structure of Input Port



14.3 TLE9844-2QX Port Implementation Details

14.3.1 Port 0

14.3.1.1 Port 0 Functions

Port 0 alternate function mapping according Table 8

Table 8 Port 0 Input/Output Functions

Port Pin	Input/Output	Select	Connected Signal(s)	From/to Module
P0.0	Input	GPI	P0_DATA.P0	
		INP1	T12HR_0	CCU6
		INP2	T4INA	GPT12
		INP3	T2_0	Timer 2
		INP4	SWD_CLK	SWD
		INP5	EXINT2_3	SCU
	Output	GPO	P0_DATA.P0	
		ALT1	T3OUT_0	GPT12
		ALT2	EXF21_0	Timer 21
		ALT3	UART2_RXDO	UART2
P0.1	Input	GPI	P0_DATA.P1	
		INP1	T13HR_0	CCU6
		INP2	UART1_RXD	UART1
		INP3	T2EX_1	Timer 2
		INP4	T21_0	Timer 21
		INP5	EXINT0_3	SCU
		INP6	T4INC	GPT12
		INP7	CAPINA	GPT12
		INP8	SSC12_S_SCK	SSC1/2
		INP9	CC62_0	CCU6
	Output	GPO	P0_DATA.P1	
		ALT1	T6OUT_0	GPT12
		ALT2	CC62_0	CCU6
		ALT3	SSC12_M_SCK	SSC1/2



Port Pin	Input/Output	Select	Connected Signal(s)	From/to Module
P0.2	Input	GPI	P0_DATA.P2	
		INP1	T2EUDA	GPT12
		INP2	CTRAP_0	CCU6
		INP3	SSC12_M_MRST	SSC1/2
		INP4	T21EX_0	Timer 21
		INP5	EXINT1_3	SCU
	Output	GPO	P0_DATA.P2	
		ALT1	SSC12_S_MRST	SSC1/2
		ALT2	UART1_TXD	UART1
		ALT3	EXF2_0	Timer 2
P0.3	Input	GPI	P0_DATA.P3	
		INP1	SSC1_S_SCK	SSC1
		INP2	T4EUDA	GPT12
		INP3	CAPINB	GPT12
		INP4	EXINT1_2	SCU
		INP5	T3EUDD	GPT12
		INP6	CCPOS0_1	CCU6
	Output	GPO	P0_DATA.P3	
		ALT1	SSC1_M_SCK	SSC1
		ALT2	T6OFL	GPT12
		ALT3	T6OUT_1	GPT12
P0.4	Input	GPI	P0_DATA.P4	
		INP1	SSC1_S_MTSR	SSC1
		INP2	CC60_0	CCU6
		INP3	T21_2	Timer 21
		INP4	EXINT2_2	SCU
		INP5	T3EUDA	GPT12
		INP6	CCPOS1_1	CCU6
	Output	GPO	P0_DATA.P4	
		ALT1	SSC1_M_MTSR	SSC1
		ALT2	CC60_0	CCU6
		ALT3	CLKOUT_0	SCU

Table 8 Port 0 Input/Output Functions (cont'd)



Port Pin	Input/Output	Select	Connected Signal(s)	From/to Module
P0.5	Input	GPI	P0_DATA.P5	
		INP1	SSC1_M_MRST	SSC1
		INP2	EXINT0_0	SCU
		INP3	T21EX_2	Timer 21
		INP4	T5INA	GPT12
		INP5	CCPOS2_1	CCU6
	Output	GPO	P0_DATA.P5	
		ALT1	SSC1_S_MRST	SSC1
		ALT2	COUT60_0	CCU6
		ALT3	LIN_RXD	LIN

Table 8 Port 0 Input/Output Functions (cont'd)



14.3.2 Port 1

14.3.2.1 Port 1 Functions

Port 1alternate function mapping according Table 9

Port Pin	Input/Output	Select	Connected Signal(s)	From/to Module
P1.0	Input	GPI	P1_DATA.P0	
		INP1	T3INC	GPT12
		INP2	CC61_0	CCU6
		INP3	SSC2_S_SCK	SSC2
		INP4	T4EUDB	GPT12
	Output	GPO	P1_DATA.P0	
		ALT1	SSC2_M_SCK	SSC2
		ALT2	CC61_0	CCU6
		ALT3	UART2_TXD	UART2
P1.1	Input	GPI	P1_DATA.P1	
		INP1	T6EUDA	GPT12
		INP2	T5INB	GPT12
		INP3	T3EUDC	GPT12
		INP4	SSC2_S_MTSR	SSC2
		INP5	T21EX_3	Timer 21
		INP6	UART2_RXD	UART2
	Output	GPO	P1_DATA.P1	
		ALT1	SSC2_M_MTSR	SSC2
		ALT2	COUT61_0	CCU6
		ALT3	EXF21_1	Timer 21
P1.2	Input	GPI	P1_DATA.P2	
		INP1	EXINT0_1	SCU
		INP2	T21_1	Timer 21
		INP3	T2INA	GPT12
		INP4	SSC2_M_MRST	SSC2
		INP5	CCPOS2_2	CCU6
	Output	GPO	P1_DATA.P2	
		ALT1	SSC2_S_MRST	SSC2
		ALT2	COUT63_0	CCU6
		ALT3	T3OUT_1	GPT12

Table 9 Port 1 Input / Output Functions



Port Pin	Input/Output	Select	Connected Signal(s)	From/to Module
P1.4	Input	GPI	P1_DATA.P4	
		INP1	EXINT2_1	SCU
		INP2	T21EX_1	Timer 21
		INP3	T2INB	GPT12
		INP4	T5EUDA	GPT12
		INP5	SSC12_S_MTSR	SSC1/2
		INP6	CCPOS1_2	CCU6
	Output	GPO	P1_DATA.P4	
		ALT1	CLKOUT_1	SCU
		ALT2	COUT62_0	CCU6
		ALT3	SSC12_M_MTSR	SSC1/2

Table 9 Port 1 Input / Output Functions (cont'd)



14.3.3 Port 2

14.3.3.1 Port 2 Functions

Port 2 alternate function mapping according Table 10

Port Pin	Input/Output	Select	Connected Signal(s)	From/to Module
P2.0	Input	GPI	P2_DATA.P0	
		INP1	EXINT1_1	SCU
		INP2	CCPOS0_2	CCU6
		INP3	T5EUDB	GPT12
		ANALOG	AN0	ADC
P2.1	Input	GPI	P2_DATA.P1	
		INP1	CCPOS0_0	CCU6
		INP2	EXINT1_0	SCU
		INP3	T12HR_1	CCU6
		INP4	CC61_1	CCU6
		ANALOG	AN1	ADC
P2.2	Input	GPI	P2_DATA.P2	
		INP1	T6EUDB	GPT12
		INP2	T2EX_0	Timer 2
		INP3	T12HR_2	CCU6
		ANALOG	AN2	ADC
P2.3	Input	GPI	P2_DATA.P3	
		INP1	CCPOS1_0	CCU6
		INP2	EXINT0_2	SCU
		INP3	CTRAP_1	CCU6
		INP4	T3IND	GPT12
		INP5	CC60_1	CCU6
		ANALOG	AN3	ADC
P2.4	Input	GPI	P2_DATA.P4	
		INP1	T2EUDB	GPT12
		INP2	T2_2	Timer 2
		INP3	T2EX_2	Timer 2
		INP4	CCPOS0_3	CCU6
		INP5	CTRAP_2	CCU6
		IN	XTAL (in) ¹⁾	XTAL

Table 10Port 2 Input Functions



Port Pin	Input/Output	Select	Connected Signal(s)	From/to Module
P2.5	Input / Output	GPI	P2_DATA.P5	
		INP1	T3EUDB	GPT12
		INP2	T4EUDC	GPT12
		INP3	T2_1	Timer 2
		INP4	LIN_TXD	LIN
		INP5	CCPOS1_3	CCU6
		OUT	XTAL (out) ¹⁾	XTAL
P2.6	Input	GPI	P2_DATA.P6	
		INP1	T4EUDD	GPT12
		INP2	T2EX_3	Timer 2
		INP3	CCPOS2_3	CCU6
		INP4	T13HR_2	CCU6
		ANALOG	AN6	ADC
P2.7	Input	GPI	P2_DATA.P7	
		INP1	CCPOS2_0	CCU6
		INP2	EXINT2_0	SCU
		INP3	T13HR_1	CCU6
		INP4	CC62_1	CCU6
		ANALOG	AN7	ADC

Table 10 Port 2 Input Functions (cont'd)

1) configurable by user



General Purpose Timer Units (GPT12)

15 General Purpose Timer Units (GPT12)

15.1 Features

15.1.1 Features Block GPT1

The following list summarizes the supported features:

- $f_{\text{GPT}}/4$ maximum resolution
- 3 independent timers/counters
- Timers/counters can be concatenated
- 4 operating modes:
 - Timer Mode
 - Gated Timer Mode
 - Counter Mode
 - Incremental Interface Mode
- Reload and Capture functionality
- Shared interrupt: Node 0

15.1.2 Features Block GPT2

The following list summarizes the supported features:

- $f_{\text{GPT}}/2$ maximum resolution
- · 2 independent timers/counters
- Timers/counters can be concatenated
- 3 operating modes:
 - Timer Mode
 - Gated Timer Mode
 - Counter Mode
- Extended capture/reload functions via 16-bit capture/reload register CAPREL
- Shared interrupt: Node 1

15.2 Introduction

The General Purpose Timer Unit blocks GPT1 and GPT2 have very flexible multifunctional timer structures which may be used for timing, event counting, pulse width measurement, pulse generation, frequency multiplication, and other purposes.

They incorporate five 16-bit timers that are grouped into the two timer blocks GPT1 and GPT2. Each timer in each block may operate independently in a number of different modes such as Gated timer or Counter Mode, or may be concatenated with another timer of the same block.

Each block has alternate input/output functions and specific interrupts associated with it. Input signals can be selected from several sources by register PISEL.

The GPT module is clocked with clock f_{GPT} . f_{GPT} is a clock derived from f_{SYS} .



General Purpose Timer Units (GPT12)

15.2.1 Block Diagram GPT1

Block GPT1 contains three timers/counters: The core timer T3 and the two auxiliary timers T2 and T4. The maximum resolution is $f_{GPT}/4$. The auxiliary timers of GPT1 may optionally be configured as reload or capture registers for the core timer.



Figure 23 GPT1 Block Diagram (n = 2 ... 5)



General Purpose Timer Units (GPT12)

15.2.2 Block Diagram GPT2

Block GPT2 contains two timers/counters: The core timer T6 and the auxiliary timer T5. The maximum resolution is $f_{GPT}/2$. An additional Capture/Reload register (CAPREL) supports capture and reload operation with extended functionality.



Figure 24 GPT2 Block Diagram (n = 1 ... 4)



Timer2 and Timer21

16 Timer2 and Timer21

16.1 Features

- 16-bit auto-reload mode
 - selectable up or down counting
- One channel 16-bit capture mode
- Baud-rate generator for U(S)ART

16.2 Introduction

Two functionally identical timers are implemented: Timer 2 and 21. The description refers to Timer 2 only, but applies to Timer 21 as well.

The timer modules are general purpose 16-bit timer. Timer 2 can function as a timer or counter in each of its modes. As a timer, it counts with an input clock of $f_{sys}/12$ (if prescaler is disabled). As a counter, Timer 2 counts 1-to-0 transitions on pin T2. In the counter mode, the maximum resolution for the count is $f_{sys}/24$ (if prescaler is disabled).

16.2.1 Timer2 and Timer21 Modes Overview

Mode	Description		
Auto-reload	Up/Down Count Disabled		
	Count up only		
	 Start counting from 16-Bit reload value, overflow at FFF_H 		
	Reload event configurable for trigger by overflow condition only, or by		
	negative/positive edge at input pin T2EX as well		
	Programmable reload value in register RC2		
	 Interrupt is generated with reload events. 		

Table 11 Port Registers



Timer2 and Timer21

Mode	Description			
Auto-reload	 Up/Down Count Enabled Count up or down, direction determined by level at input pin T2EX No interrupt is generated Count up Start counting from 16-Bit reload value, overflow at FFFF_H Reload event triggered by overflow condition Programmable reload value in register RC2 Count down Start counting from FFFF_H, underflow at value defined in register RC2 Reload event triggered by underflow condition Reload event triggered by underflow at value defined in register RC2 			
Channel capture	 Count up only Start counting from 0000_H, overflow at FFFF_H Reload event triggered by overflow condition Reload value fixed at 0000_H Capture event triggered by falling/rising edge at pin T2EX Captured timer value stored in register RC2 Interrupt is generate with reload or capture event 			

Table 11Port Registers (cont'd)



17 Capture/Compare Unit 6 (CCU6)

17.1 Feature Set Overview

This section gives an overview over the different building blocks and their main features.

Timer 12 Block Features

- Three capture/compare channels, each channel can be used either as capture or as compare channel
- Generation of a three-phase PWM supported (six outputs, individual signals for High Side and low-side switches)
- 16-bit resolution, maximum count frequency = peripheral clock
- Dead-time control for each channel to avoid short-circuits in the power stage
- Concurrent update of T12 registers
- · Center-aligned and edge-aligned PWM can be generated
- Single-shot mode supported
- Start can be controlled by external events
- Capability of counting external events
- Multiple interrupt request sources
- Hysteresis-like control mode

Timer 13 Block Features

- One independent compare channel with one output
- 16-bit resolution, maximum count frequency = peripheral clock
- Concurrent update of T13 registers
- Can be synchronized to T12
- Interrupt generation at period-match and compare-match
- Single-shot mode supported
- · Start can be controlled by external events
- · Capability of counting external events

Additional Specific Functions

- Block commutation for Brushless DC-drives implemented
- Position detection via Hall-sensor pattern
- Noise filter supported for position input signals
- · Automatic rotational speed measurement and commutation control for block commutation
- Integrated error handling
- Fast emergency stop without CPU load via external signal (CTRAP)
- Control modes for multi-channel AC-drives
- Output levels can be selected and adapted to the power stage

17.2 Introduction

The CCU6 unit is made up of a Timer T12 Block with three capture/compare channels and a Timer T13 Block with one compare channel. The T12 channels can independently generate PWM signals or accept capture triggers, or they can jointly generate control signal patterns to drive AC-motors or inverters.

A rich set of status bits, synchronized updating of parameter values via shadow registers, and flexible generation of interrupt request signals provide means for efficient software-control.

Note: The capture/compare module itself is named CCU6 (capture/compare unit 6). A capture/compare channel inside this module is named CC6x.



Capture/Compare Unit 6 (CCU6)

17.2.1 Block Diagram

The Timer T12 can work in capture and/or compare mode for its three channels. The modes can also be combined (e.g. a channel works in compare mode, whereas another channel works in capture mode). The Timer T13 can work in compare mode only. The multi-channel control unit generates output patterns which can be modulated by T12 and/or T13. The modulation sources can be selected and combined for the signal modulation.



Figure 25 CCU6 Block Diagram



UART1/UART2

18 UART1/UART2

18.1 Features

- Full-duplex asynchronous modes
 - 8-Bit or 9-Bit data frames, LSB first
 - fixed or variable baud rate
- Receive buffered (1 Byte)
- Multiprocessor communication
- Interrupt generation on the completion of a data transmission or reception
- Baud-rate generator with fractional divider for generating a wide range of baud rates, e.g. 9.6kBaud, 19.2kBaud, 115.2kBaud, 125kBaud, 250kBaud, 500kBaud
- · Hardware logic for break and sync byte detection
- for UART1: LIN support: connected to timer channel for synchronization to LIN baud rate

In all modes, transmission is initiated by any instruction that uses SBUF as a destination register. Reception is initiated in the modes by the incoming start bit if REN = 1.

The serial interface also provides interrupt requests when transmission or reception of the frames has been completed. The corresponding interrupt request flags are TI or RI, respectively. If the serial interrupt is not used (i.e., serial interrupt not enabled), TI and RI can also be used for polling the serial interface.

18.2 Introduction

The UART1/UART2 provide a full-duplex asynchronous receiver/transmitter, i.e., it can transmit and receive simultaneously. They are also receive-buffered, i.e., they can commence reception of a second byte before a previously received byte has been read from the receive register. However, if the first byte still has not been read by the time reception of the second byte is complete, the previous byte will be lost. The serial port receive and transmit registers are both accessed at Special Function Register (SFR) SBUF. Writing to SBUF loads the transmit register, and reading SBUF accesses a physically separate receive register.



UART1/UART2

18.2.1 Block Diagram



Figure 26 UART Block Diagram

18.3 UART Modes

The UART1/UART2 can be used in four different modes. In mode 0, it operates as an 8-Bit shift register. In mode 1, it operates as an 8-Bit serial port. In modes 2 and 3, it operates as a 9-Bit serial port. The only difference between mode 2 and mode 3 is the baud rate, which is fixed in mode 2 but variable in mode 3. The variable baud rate is set by the underflow rate on the dedicated baud-rate generator.

The different modes are selected by setting bits SM0 and SM1 to their corresponding values, as shown in Table 12.

Mode 1 example: 8 data bits, 1 start bit, 1 stop bit, no parity selection, 16 times oversampled (majority decision of bits 6, 7, 8), receive & transmit register double buffered, Tx/Rx IRQ(s).

SM0	SM1	Operating Mode	Baud Rate
0	0	Mode 0: 8-Bit shift register	f _{sys} /2
0	1	Mode 1: 8-Bit shift UART	Variable
1	0	Mode 2: 9-Bit shift UART	$f_{\rm sys}$ /64 or $f_{\rm sys}$ /32
1	1	Mode 3: 9-Bit shift UART	Variable

Table 12 UART Modes



LIN Transceiver

19 LIN Transceiver

19.1 Features

General Functional Features

- Compliant to LIN2.2 Standard, backward compatible to LIN1.3, LIN2.0 and LIN 2.1
- Compliant to SAE J2602 (Slew Rate, Receiver hysteresis)

Special Features

- Measurement of LIN Master baudrate via Timer 2
- LIN can be used as Input/Output with SFR bits.
- TxD Timeout Feature (optional, on by default)
- Overcurrent limitation and overtemperature protection
- · LIN module fully resettable via global enable bit

Operation Modes Features

- LIN Sleep Mode (LSLM)
- LIN Receive-Only Mode (LROM)
- LIN Normal Mode (LNM)
- High Voltage Input / Output Mode (LHVIO)

Slope Modes Features

- Normal Slope Mode (20 kbit/s)
- Low Slope Mode (10.4 kbit/s)
- Fast Slope Mode (62.5 kbit/s)
- Flash Mode (115 kbit/s, 250 kbit/s)

Wake-Up Features

LIN Bus wake-up. The wake-up happens on the falling edge of the LIN signal, to allow wake-up and decoding
of the same frame. It is possible to enter the sleep mode also with LIN dominant (e.g. caused by LIN shorted
to GND).

19.2 Introduction

The LIN Module is a transceiver for the Local Interconnect Network (LIN) compliant to the LIN2.2 Standard, backward compatible to LIN1.3, LIN2.0 and LIN2.1. It operates as a bus driver between the protocol controller and the physical network. The LIN bus is a single wire, bi-directional bus typically used for in-vehicle networks, using baud rates between 2.4 kBaud and 20 kBaud. Additionally baud rates up to 62.5 kBaud are implemented.

The LIN Module offers several different operation modes, including a LIN Sleep Mode and the LIN Normal Mode. The integrated slope control allows to use several data transmission rates with optimized EMC performance. For data transfer at the end of line, a Flash Mode up to 115 kBaud is implemented. This Flash Mode can be used for data transfer under special conditions for up to 250 kbit/s (in production environment, point-to-point communication with reduced wire length and limited supply voltage).



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LIN Transceiver

19.2.1 Block Diagram



Figure 27 LIN Transceiver Block Diagram



High-Speed Synchronous Serial Interface SSC1/SSC2

20 High-Speed Synchronous Serial Interface SSC1/SSC2

20.1 Features

- Master and Slave Mode operation
 - Full-duplex or half-duplex operation
 - Transmit and receive double buffered
- Flexible data format
 - Programmable number of data bits: 2 to 16 bits
 - Programmable shift direction: Least Significant Bit (LSB) or Most Significant Bit (MSB) shift first
 - Programmable clock polarity: idle low or high state for the shift clock
 - Programmable clock/data phase: data shift with leading or trailing edge of the shift clock
- Variable baud rate, e.g. 250kBaud 8MBaud
- Compatible with Serial Peripheral Interface (SPI)
- Interrupt generation
 - On a transmitter empty condition
 - On a receiver full condition
 - On an error condition (receive, phase, baud rate, transmit error)
 - On a transfer complete condition
- Port direction selection, see Chapter 14

20.2 Introduction

The High-Speed Synchronous Serial Interface (SSC) supports both full-duplex and half-duplex serial synchronous communication. The serial clock signal can be generated by the SSC internally (master mode), using its own 16-Bit baud-rate generator, or can be received from an external master (slave mode). Data width, shift direction, clock polarity, and phase are programmable. This allows communication with SPI-compatible devices or devices using other synchronous serial interfaces.

Data is transmitted or received on lines TXD and RXD, which are normally connected to the pins MTSR (MasterTransmit/Slave Receive) and MRST (Master Receive/Slave Transmit). The clock signal is output via line MS_CLK (Master Serial Shift Clock) or input via line SS_CLK (Slave Serial Shift Clock). Both lines are normally connected to the pin SCLK. Transmission and reception of data are double-buffered.



High-Speed Synchronous Serial Interface SSC1/SSC2

20.2.1 Block Diagram

Figure 28 shows all functional relevant interfaces associated with the SSC Kernel.



Figure 28 SSC Interface Diagram



21 Measurement Unit

21.1 Features

- 1 x 10 Bit ADC with 13 Inputs including attenuator allowing measurement of high voltage input signals
- Supply Voltage Attenuators with attenuation of VBAT_SENSE, VS, MONx, P2.x.
- 1 x 8 Bit ADC with 7 Inputs including attenuator allowing measurement of high voltage input signals
- Supply Voltage Attenuators with attenuation of VS, VDDEXT, VDDP, VBG, VDDC, TSENSE_LS, TSENSE_CENTRAL.
- VBG monitoring of 8 Bit ADC to support functional safety requirements.
- Temperature Sensor for monitoring the chip temperature and Low Side module temperature.
- Supplement Block with Reference Voltage Generation, Bias Current Generation, Voltage Buffer for NVM Reference Voltage, Voltage Buffer for Analog Module Reference Voltage and Test Interface.

21.2 Introduction

The measurement unit is a functional unit that comprises the following associated sub-modules:

Module Name	Modules	Functions
Central Functions Unit	Bandgap reference circuit + current reference circuit	The bandgap-reference sub-module provides two reference voltages 1. an accurate reference voltage for the 10-bit and 8-bit ADCs. A local dedicated bandgap circuit is implemented to avoid deterioration of the reference voltage arising e.g. from crosstalk or ground voltage shift. 2. the reference voltage for the NVM module
10 Bit ADC (ADC1)	10-bit ADC module with 13 multiplexed analog inputs	VBAT_SENSE, VS and MONx measurement. Six (5V) analog inputs from Port 2.x
8 Bit ADC (ADC2)	8-bit ADC module with 7 multiplexed inputs	VS/VDDEXT/VDDP/VBG/VDDC/TSENSE_LS and TSENSE_CENTRAL measurement.
Temperature Sensor	Temperature sensor readout amplifier with two multiplexed ΔV besensing elements	Generates outputs voltage which is a linear function of the local chip (Tj) temperature.
Measurement Core Module	Digital signal processing and ADC control unit	 Generates the control signal for the 8-bit ADC 2 and the synchronous clock for the switched capacitor circuits (temperature sensor) Performs digital signal processing functions and provides status outputs for interrupt generation.

 Table 13
 Measurement functions and associated modules

21.2.1 Block Diagram

The Structure of the Measurement Functions Module is shown in the following figure.


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Measurement Unit



Figure 29 TLE9844-2QX Measurement Unit-Overview



Measurement Core Module (incl. ADC2)

22 Measurement Core Module (incl. ADC2)

22.1 Features

- 7 individually programmable channels split into two groups of user configurable and non user configurable
- · Individually programmable channel prioritization scheme for measurement unit
- Two independent filter stages with programmable low-pass and time filter characteristics for each channel
- Two channel configurations:
 - Programmable upper- and lower trigger thresholds comprising a fully programmable hysteresis
 - Two individually programmable trigger thresholds with limit hysteresis settings
- Individually programmable interrupts and status for all channel thresholds
- Operation down to reset threshold of entire system

22.2 Introduction

The basic function of this block is the digital postprocessing of several analog digitized measurement signals by means of filtering level comparison and interrupt generation. The measurement postprocessing block is built of seven identical channel units attached to the outputs of the 7-channel 8-bit ADC (ADC2). It processes seven channels, where the channel sequence and prioritization is programmable within a wide range.





Figure 30 Module Block Diagram



10-Bit Analog Digital Converter (ADC1)

23 10-Bit Analog Digital Converter (ADC1)

23.1 Features

The basic function of this block is the digital postprocessing of several analog digitized measurement signals by means of filtering, level comparison and interrupt generation. The measurement postprocessing block is built of twelve identical channel units attached to the outputs of the 13-channel 10-bit ADC. It processes twelve channels, where the channel sequence and prioritization is programmable within a wide range.

Functional Features

- 10 Bit SAR ADC with conversion time of 17 clock cycles
- Programmable clock divider for sequencer and ADC
- 12 individually programmable channels (ch0..ch11):
 - 7 HV Channels: VS, VBAT_SENSE, MON1...MON4, MON5
 - 5 LV Channels: P2.1, P2.2, P2.3, P2.6, P2.7
- One additional channel, ch12, connected to P2.0. This channel is only programmable in software mode, no calibration and no digital postprocessing are available in this case.
- All channels are fully calibrated and user configurable
- Individually programmable channel prioritization scheme for digital postprocessing (dpp)
- Two independent filter stages with programmable low-pass and time filter characteristics for each channel
- Two channel configurations:
 - Programmable upper- and lower trigger thresholds comprising a fully programmable hysteresis
 Two individually programmable trigger thresholds with limit hysteresis settings
- Individually programmable upper threshold and lower threshold interrupts and status for all channel thresholds
- ADC reference completely integrated

Note: In case the MONx should be evaluated by the ADC1, it is recommended to add 6.8nF capacitors close to the MONx pin of the device, in order to build an external RC filter to limit the bandwidth of the input signal.



TLE9844-2QX

10-Bit Analog Digital Converter (ADC1)

23.2 Introduction

23.2.1 Block Diagram



Figure 31 Module Block Diagram



High-Voltage Monitor Input

24 High-Voltage Monitor Input

24.1 Features

Features

- 5 High-voltage inputs with VS/2 threshold voltage
- Wake capability for system stop mode and system sleep mode
- · Edge sensitive wake-up feature configurable for transitions from low to high, high to low or both directions
- MON inputs can also be evaluated with ADC in Active Mode, using adjustable threshold values (see also Chapter 23).
- Selectable pull-up and pull-down current sources available

24.2 Introduction

This module is dedicated to monitor external voltage levels above or below a specified threshold. Each MONx pin can further be used to detect a wake-up event by detecting a level change by crossing the selected threshold. This applies to any power mode. Further more each MONx pin can be sampled by the ADC as analog input.

24.2.1 Block Diagram







High-Side Switch

25 High-Side Switch

25.1 Features

The high-side switch is optimized for driving resistive loads. Only small line inductance are allowed. Typical applications are single or multiple LEDs of a dashboard, switch illumination or other loads that require a high-side switch.

A cyclic switch activation during Sleep Mode or Stop Mode of the system is also available.

Functional Features

- Multi-purpose high-side switch for resistive load connections (only small line inductances are allowed)
- Overcurrent limitation
- Overcurrent detection with thresholds: 25 mA, 50 mA, 100 mA, 150 mA and automatic shutdown
- Overtemperature detection and automatic shutdown
- Open load detection in on mode with open load current of max. 1.5 mA.
- Interrupt signalling of overcurrent, overtemperature and open load condition
- Cyclic switch activation in Sleep Mode and Stop Mode with cyclic sense support and reduced driver capability: max. 40 mA
- PWM capability up to 25 kHz
- Internal connection to System-PWM Generator (CCU6)
- Slew rate control for low EMI characteristic

Applications hints

• The voltage at HSx must not exceed the supply voltage by more than 0.3V to prevent a reverse current from HSx to VS.



High-Side Switch

25.2 Introduction

25.2.1 Block Diagram



Figure 33 High-Side Module Block Diagram (incl. subblocks)

25.2.2 General

The high-side switch can generally be controlled in three different ways:

- In Normal mode the output stage is fully controllable through the **SFR** Registers **HSx_CTRL**. Protection functions as overcurrent, overtemperature and open load detection are available.
- The PWM Mode can also be enabled by a HSx_CTRL SFR bit. The PWM configuration has to be done in the corresponding PWM Module. All protection functions are also available in this mode. The maximum PWM frequency must not exceed 25 kHz (disabled slew rate control only).
- The high-side switch provides also the possibility of cyclic switch activation in all low power modes (Sleep Mode and Stop Mode). In this configuration it has limited functionality with limited current capability. Diagnostic functions are not available in this mode.



Low-Side Switch

26 Low-Side Switch

26.1 Features

The general purpose low-side switch is optimized to control an on-board relay. The low-side switch provides embedded protection functions including overcurrent and overtemperature detection. The module is designed for on-board connections.

Measures for standard ESD (HBM) and EMC robustness are implemented.

Functional Features

- Multi purpose low-side switch optimized for driving relays:
 - simple relay driver
 - PWM relay driver
- Integrated clamping for usage as a simple relay driver
- overcurrent detection and automatic shutdown
- overtemperature detection and automatic shutdown
- · interrupt signalling of overcurrent and overtemperature condition
- open load detection with interrupt signalling
- PWM capability up to 25 kHz (for inductive loads with external clamping circuitry only!)
- Selectable PWM source: dedicated CCU6 channels
- Current drive capability up to min. 270 mA

Applications hints

• It is not recommended to use the switch in PWM Mode without external free wheeling diode.



TLE9844-2QX

Low-Side Switch



Figure 34 Module Block Diagram

26.2 Functional Description

The low-side switches can generally be controlled in two different ways:

- In normal mode the output stage is fully controllable through the **SFR** Registers **LSx_CTRL**. Protection functions as overcurrent and overtemperature are available.
- The PWM Mode can also be enabled by a LSx_CTRL SFR bit. The PWM configuration has to be done in the corresponding PWM Module (CCU6). All protection functions are also available in this mode. The maximum PWM frequency must not exceed 25 kHz (fast slew rate only).



Note: The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device.

27.1 Relay Window Lift Application diagram



Figure 35 Simplified Application Diagram Example

Note: This is a very simplified example of an application circuit and bill of material. The function must be verified in the actual application.



Symbol	Function	Component
C _{1VS}	Capacitor 1 at VS pin	22 µF ¹⁾
C _{2VS}	Capacitor 2 at VS pin	100 nF ²⁾³⁾
C _{VDDEXT}	Capacitor at VDDEXT pin	330 nF ²⁾
C _{VDDC}	Capacitor at VDDC pin	100 nF ²⁾³⁾ + 330 nF ²⁾
C _{VDDP}	Capacitor at VDDP pin	470 nF ²⁾³⁾ + 470 nF ²⁾
R _{MONx}	Resistor at MONx pin	3.9 kΩ
C _{MONx}	Capacitor at MONx connector	6.8 nF ⁴⁾
R _{VBAT_SENSE}	Resistor at VBAT_SENSE pin	3.9 kΩ
C _{VBAT_SENSE1}	Capacitor 1at VBAT_SENSE pin	10 nF ²⁾
C _{VBAT_SENSE2}	Capacitor 2 at VBAT_SENSE connector	6.8 nF ⁴)
C _{LIN}	Capacitor at LIN pin	220 pF
R _{1HS}	Resistor at HS pin for LED	e.g. 2.7kΩ
R _{2HS}	Resistor at HS pin	160 Ω ⁵⁾
C _{1HS}	Capacitor at HS pin	6.8nF ²⁾
C _{2HS}	Capacitor at HS connector	33nF ⁴⁾

Table 14 External Component (BOM)

1) to be dimensioned according to application requirements

2) to reduce the effect of fast voltage transients of Vs, these capacitors should be placed close to the device pin

- 3) ceramic capacitor
- 4) for ESD GUN
- 5) optional, for short to battery protection, calculated for 24V (jump start)

27.2 Connection of N.C.

The device contains several N.C. (not connected, no bond wire).

 Table 15
 Recommendation for connecting N.C. / N.U. pins

type	pin number	recommendation 1	recommendation 2	comment
N.C.	27, 28, 29, 38, 40, 41	GND		
N.C.	10, 46	open	GND	neighboring high-voltage pins

27.3 Connection of unused pins

Table 16 shows recommendations how to connect pins, in case they are not needed by the application.

Table 16Recommendation for connecting unused pins

type	pin number	recommendation 1 (if unused)	recommendation 2 (if unused)
LIN	1	open	
HS1, HS2	3, 4	VS	open



type	pin number	recommendation 1 (if unused)	recommendation 2 (if unused)
MON	5, 6, 7, 8, 9	GND	open + configure internal PU/PD
LS1, LS2	11, 12	GNDLS	open
GPIO	14, 15, 16, 17, 20, 22, 23, 24, 25, 26, 33, 34, 35, 36, 37, 39	GND	external PU/PD or open + configure internal PU/PD
TMS	18	GND	
Reset	21	open	
P2/XTAL out	31	open	
P2/XTAL in	32	GND	
VDDEXT	45	open	
VBAT_SENSE	48	VS	

Table 16 Recommendation for connecting unused pins

27.4 Connection of P0.2 for SWD debug mode

To enter the SWD debug mode, P0.2 needs to be 0 at the rising edge of the reset signal.

P0.2 has an internal pulldown, so it just needs to be ensured that there is no external 1 at P0.2 when the debug mode is entered.

27.5 Connection of TMS

For the debug mode, the TMS pin needs to be 1 at the rising edge of the reset signal. This is controlled by the debugger. The TMS pin has an internal PD.

To avoid the device entering the debug mode unintendedly in the final application, adding an external pull-down additionally is recommended.

27.6 ESD Immunity According to IEC61000-4-2

Note: Tests for ESD robustness according to IEC61000-4-2 "gun test" (150pF, 330Ω) were performed. The results and test condition are available in a test report. The achieved values for the test are listed in **Table 17** below.

Performed Test	Result	Unit	Remarks
ESD at pin LIN, versus GND	≥6	kV	¹⁾ positive pulse
ESD at pin LIN, versus GND	≤ -6	kV	¹⁾ negative pulse
ESD at pin VS, VBAT_SENSE, MONx, HS, versus GND	≥6	kV	¹⁾ positive pulse
ESD at pin VS, VBAT_SENSE, MONx, HS, versus GND	≤ -6	kV	¹⁾ negative pulse

Table 17 ESD "Gun Test"



 ESD susceptibility "ESD GUN", tested by external test house (IBEE Zwickau, EMC Test report Nr. 11-01-16), according to "LIN Conformance Test Specification Package for LIN 2.1, October 10th, 2008" and "Hardware Requirements for LIN, CAN and FlexRay Interfaces in Automotive Application – AUDI, BMW, Daimler, Porsche, Volkswagen – Revision 1.3 / 2012"



28 Electrical Characteristics

This chapter includes all relevant Electrical Characteristics of the product TLE9844-2QX.

28.1 General Characteristics

28.1.1 Absolute Maximum Ratings

Table 18 Absolute Maximum Ratings¹⁾

 $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	S	Unit		Number	
		Min.	Тур.	Max.		Test Condition		
Voltages Supply Pins							1	
VS voltage	$V_{\mathrm{S,max}}$	-0.3	-	40	V	Load dump	P_1.1.1	
VDDP voltage	$V_{\rm DDP,max}$	-0.3	-	5.5	V	-	P_1.1.2	
VDDEXT voltage	V _{DDEXT,max}	-0.3	-	V _S +0.3	V	-	P_1.1.3	
VDDC voltage	$V_{\rm DDC,max}$	-0.3	-	1.6	V	-	P_1.1.4	
Voltages High Voltage Pins						1		
Voltage at VBAT_SENSE pin	$V_{\rm BAT_SENSE,}$ max	-28	-	40	V	2)	P_1.1.5	
Voltage at HS pin	$V_{\rm HS,max}$	-0.3	-	V _S +0.3	V	-	P_1.1.6	
Voltage at LIN pin	$V_{\rm LIN,max}$	-28	-	40	V	-	P_1.1.7	
Voltage at MON_x pins	$V_{\rm MON,max}$	-28	-	40	V	2)	P_1.1.8	
Voltage at LS pin	$V_{\rm LS,max}$	-0.3	-	40	V	Internal clamping structure > 40V	P_1.1.9	
Voltages GPIOs			1		1	1	1	
Voltage on port pin P0.x, P1.x, P2.x, TMS and RESET	$V_{\rm IO,max}$	-0.3	-	V _{DDP} +0.3	V	$V_{\rm IN} < V_{\rm DDPmax}^{3)}$	P_1.1.10	
Currents		-•				-	. <u>,</u>	
Injection current in Sleep Mode on P0.x, P1.x, P2.x, TMS and RESET	I _{xx}	_	-	5	mA	maximum allowed injection current on single pin or sum of pins in Sleep Mode and unpowered device	P_1.1.11	
Injection current on HS	I _{XLO}	-	-	150	mA	current flowing into HS pin (back supply in case of short to bat- tery)	P_1.1.12	



Table 18Absolute Maximum Ratings¹ (cont'd)

 $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol Values			s	Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
Output current on LS	I _{LS}	-300	-	-	mA	current flowing out of LS pin, e.g. reverse polarity event (defined in LV124) or ISO Pulse event (defined in ISO 7637-2)	P_1.1.13
Temperatures	. <u>.</u>		*				- <u>!</u>
Junction Temperature	Tj	-40	-	150	°C	-	P_1.1.14
Storage Temperature	T_{stg}	-55	-	150	°C	_	P_1.1.15
ESD Susceptibility							
ESD Susceptibility HBM all pins	V _{ESD1}	-2	-	2	kV	JEDEC HBM ⁴⁾	P_1.1.16
ESD Susceptibility HBM pins LIN vs. LINGND	V _{ESD3}	-6	-	6	kV	JEDEC HBM ⁴⁾	P_1.1.17
ESD Susceptibility CDM	V _{ESD_CDM}	-500	_	500	V	Charged device model, acc. JEDEC JESD22-C101	P_1.1.18
ESD Susceptibility CDM pins 1, 12, 13, 24, 25, 36, 37, 48 (corner pins)	V _{ESD_CDM}	-750	-	750	V	Charged device model, acc. JEDEC JESD22-C101	P_1.1.19

1) Not subject to production test, specified by design.

2) for -28V, external $3.9k\Omega$ resistor is required to limit output current.

3) One of these limits must be kept. Keeping V

4) ESD susceptibility, "JEDEC HBM" according to ANSI/ESDA/JEDEC JS001 (1.5kΩ, 100pF).

Notes

- 1. Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
- 2. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

28.1.2 Functional Range

Note: Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.



Table 19Functional Range

 $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	S	Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
Supply voltage in Active Mode	V_{S_AM}	5.5	_	28	V	_	P_1.2.1
Extended Supply voltage in Active Mode - Range 1	V _{S_AM_exte} nd_1	28	-	40	V	Functional with parameter deviation ¹⁾	P_1.2.12
Extended Supply voltage in Active Mode with reduced functionality (Microcontroller / Flash with full operation) - Range 2	V _{S_AM_exte} nd_2	3.0	-	5.5	V	Functional with parameter deviation ²⁾	P_1.2.2
Specified Supply voltage for LIN Transceiver - Active Mode	$V_{\rm S_AM_LIN}$	5.5	-	18	V	Parameter Specification	P_1.2.3
Extended Supply voltage for LIN Transceiver - Active Mode	$V_{\rm S_AM_LIN_}$ extend	4.8	-	28	V	Functional with parameter deviation	P_1.2.4
Extended Supply voltage for LIN & Monitoring Input (MON) - Stop & Sleep Mode	V _{S_SSM_LIN} _MON_extend	3.6	-	5.5	V	Wakeup functionality ensured	P_1.2.13
Min. Supply voltage in Stop Mode	$V_{\rm S_Stopmin}$	3.0	-	-	V		P_1.2.5
Min. Supply voltage in Sleep Mode	$V_{\rm S_Sleepmin}$	3.0	-	-	V		P_1.2.6
Supply Voltage transients slew rate	dV_S/dt	-5	-	5	V/µs	3)	P_1.2.7
Output current on any GPIO	$I_{\rm OH}$, $I_{\rm OL}$	-10	_	10	mA	3)	P_1.2.8
Output sum current for all GPIO pins	$I_{\rm GPIO,sum}$	-50	-	50	mA	3)	P_1.2.9
Operating frequency	$f_{\rm sys}^{4)}$	5	-	40	MHz	3)	P_1.2.10
Junction Temperature	Tj	-40	-	150	°C	-	P_1.2.11

1) This operation voltage range is only allowed for a short duration: $t_{max} \le 400$ ms.

 Hall-Supply, ADC, SPI, UART, NVM, RAM, CPU fully functional and in spec down to 3V VS. Actuators (HS, LS) in VS range from 3V < VS < 5.5V functional but some parameters can be out of spec

3) Not subject to production test, specified by design.

4) Function not specified when limits are exceeded.

28.1.3 Current Consumption



Table 20 Electrical Characteristics

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	s	Unit	Note / Test Condition	Number	
		Min.	Тур.	Max.				
Current Consumption (ĝVS pin							
Current Consumption in Active Mode	I _{Vs}	_	19	22	mA	fsys = 40 MHz $V_{\rm s}$ = 5.5V to 28V all digital modules enabled and functional, ADCs converting in sequencer mode, PLL running, no loads on GPIOs, VDDEXT off, LIN in recessive state (no communication), HSx & LSx enabled but off	P_1.3.18	
Current Consumption in Active Mode	I _{Vs_freduced}	_	-	15	mA	fsys = 10 MHz V_s = 13.5V all digital modules enabled and functional, ADCs converting in sequencer mode, PLL running, no loads on GPIOs, VDDEXT off, LIN in recessive state (no communication), HSx & LSx enabled but off ¹⁾	P_1.3.1	
Current consumption in Sleep Mode	I _{Sleep}	-	-	15	μΑ	System in Sleep Mode, microcontroller not powered, Wake capable via LIN and MON; GPIOs open (no loads) or connected to GND: $T_J = -40^{\circ}$ C to 25°C; $V_s = 13.5$ V	P_1.3.2	
Current consumption in Sleep Mode (extended Temperature Range)	$I_{\mathrm{Sleep}(\mathrm{T_exte})}$ nd)	-	-	25	μΑ	System in Sleep Mode, microcontroller not powered, Wake capable via LIN and MON; GPIOs open (no loads) or connected to GND: $T_{\rm J}$ = 25°C to 85°C; $V_{\rm s}$ = 13.5V	P_1.3.3	
Current consumption in Sleep Mode (extended Voltage and Temperature Range)	I _{Sleep} (V_T_e xtend)	_	_	30	μA	System in Sleep Mode, microcontroller not powered, Wake capable via LIN and MON; GPIOs open (no loads) or connected to GND: T_J = -40°C to 85°C; V_s = 5.5V to 18V	P_1.3.4	



Table 20 Electrical Characteristics (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	es	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Current consumption in Sleep Mode (extended Voltage and Temperature Range 2)	I _{Sleep(V_T_e} xtend2)	_	-	40	μA	System in Sleep Mode, microcontroller not powered, Wake capable via LIN and MON; GPIOs open (no loads) or connected to GND: $T_{\rm J}$ = -40°C to 85°C; $V_{\rm s}$ = 3V to 28V	P_1.3.7
Current consumption in Sleep Mode with cyclic wake	I _{Cyclic}	-	-	15	μA	$T_{\rm J}$ = -40°C to 25°C; $V_{\rm s}$ = 13.5V during sleep period	P_1.3.5
Current consumption in Sleep Mode with cyclic wake (extended Temperature Range)	I _{Cyclic(T_exte} nd)	_	-	30	μA	$T_{\rm J}$ = 25°C to 85°C; $V_{\rm s}$ = 13.5V; during sleep period	P_1.3.6
Current consumption in Stop Mode	I _{Stop}	-	65	115	μA	System in Stop Mode, microcontroller not clocked, Wake capable via LIN and MON; GPIOs open (no loads) or connected to GND; $T_J = -$ 40°C to 85°C	P_1.3.19
Current consumption in Stop Mode	I _{Stop_V_exte} nd	-	3.5	4.0	mA	System in Stop Mode, microcontroller not clocked, Wake capable via LIN and MON; GPIOs open (no loads) or connected to GND; $T_J = -$ 40°C to 85°C; $V_s = 3V$	P_1.3.21
Current consumption in Stop Mode with cyclic sense	I _{Stop_CS}	-	70	125	μΑ	System in Stop Mode (during stop period), microcontroller not clocked, Wake capable via LIN and MON; VDDEXT off; High Side off; GPIOs open (no loads) or connected to GND or VDDP; $T_J = -$ 40°C to 85°C; $V_s = 5.5V$ to 28V	P_1.3.20

1) Not subject to production test, specified by design

28.1.4 Thermal Resistance



Table 21Thermal Resistance

Parameter	Symbol	Symbol Values			Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
Junction to Case	$R_{\rm th(JC)}$	-	6	-	K/W	¹⁾ measured to Exposed Pad	P_1.4.1
Junction to Ambient	$R_{\rm th(JA)}$	_	33	-	K/W	2)	P_1.4.2

1) Not subject to production test, specified by design.

According to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board. Board: 76.2x114.3x1.5mm³ with 2 inner copper layers (35µm thick), with thermal via array under the exposed pad contacting the first inner copper layer and 300mm2 cooling area on the bottom layer (70µm).

28.1.5 Timing Characteristics

The transition times between the system modes are specified here. Generally the timings are defined from the time when the corresponding Bits in register PMCON0 are set until the sequence is terminated.

Table 22System Timing¹⁾

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	bol Values		es	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Wake-up over battery	t _{start}	-	-	1	ms	Battery ramp-up till MCU reset is released; Vs > 3V and RESET = '1'	P_1.5.1
Sleep-Exit	t _{sleep} - exit	-	-	1	ms	rising/falling edge of any wake-up signal (LIN, MON) till MCU software running	P_1.5.2
Sleep-Entry	t _{sleep -} entry	-	-	330	μs	2)	P_1.5.3

1) Not subject to production test, specified by design.

2) Wake events during Sleep-Entry are stored and lead to wake-up after Sleep Mode is reached.



28.2 Power Management Unit (PMU)

This chapter includes all electrical characteristics of the Power Management Unit

28.2.1 PMU Input Voltage VS

Table 23 Electrical Characteristics

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values		Unit	Note / Test Condition	Number	
		Min.	Тур.	Max.			
Required decoupling capacitance	C _{VS1}	0.1	-	-	μF	¹⁾ ESR < 1Ω	P_2.1.12
Required buffer capacitance for stability (load jumps)	$C_{\rm VS2}$	10	-	-	μF	2)	P_2.1.13

1) only min. value is tested.

2) Not subject to production test, specified by design.

28.2.2 PMU I/O Supply Parameters VDDP

Table 24 Electrical Characteristics

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition	Number	
		Min.	Тур.	Max.				
Specified Output Current	I _{VDDP}	0	-	50	mA	2)	P_2.1.1	
Required decoupling capacitance	$C_{\rm VDDP1}$	0.47	-	-	μF	³⁾⁴⁾ ESR < 1Ω	P_2.1.2	
Required buffer capacitance for stability (load jumps)	$C_{\rm VDDP2}$	0.47	-	1	μF	4)5)	P_2.1.3	
Output Voltage including line and load regulation @ Active Mode	V _{DDPOUT}	4.9	5.0	5.1	V	⁶⁾ I_{load} < 90mA;Vs > 5.5V	P_2.1.4	
Output Voltage including line and load regulation @ Stop Mode	V _{DDPOUTS}	4.5	5.0	5.25	V	⁶⁾ I_{load} is only internal;Vs > 5.5V	P_2.1.5	
Output Drop	Vs _{V DDPout}	-	50	+400	mV	⁷⁾ I_{VDDP} = 50mA; V_{S} = 3V;	P_2.1.6	
Load Regulation	V _{VDDPLOR}	-50	-	50	mV	2 90mA; C = C _{VDDP1} +C _{VDDP2}	P_2.1.7	
Line Regulation	V _{VDDPLIR}	-50	-	50	mV	V _s = 5.5 28V	P_2.1.8	
Over Voltage Detection	V _{DDPOV}	5.14	-	5.4	V	V_{s} > 5.5V; Overvoltage leads to SUPPLY_NMI	P_2.1.9	



Table 24 Electrical Characteristics (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)¹⁾

Parameter	Symbol		Values			Note / Test Condition	Number	
		Min.	Тур.	Max.				
Under Voltage Reset	V _{DDPUV}	2.55	2.7	2.8	V	-	P_2.1.10	
Over Current Diagnostic	I _{VDDPOC}	90	-	200	mA	current including VDDC current consumption	P_2.1.11	

1) currents used in this table are positive but flowing out the pin VDDP

2) Specified output current for port supply and additional other external loads connected to VDDP, excluding on-chip current consumption.

- 3) only min. value is tested.
- 4) the total capacitance on VDDP must not exceed 2,2 μ F
- 5) Not subject to production test, specified by design.
- 6) Load current includes internal supply.
- 7) Output drop for I_{VDDP} plus internal supply



28.2.3 PMU Core Supply Parameters VDDC

Table 25 Electrical Characteristics

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	S	Unit	Note /	Number	
		Min.	Тур.	Max.		Test Condition		
Required decoupling capacitance	$C_{\rm VDDC1}$	0.1	-	_	μF	¹⁾ ESR < 1Ω	P_2.2.1	
Required buffer capacitance for stability (load jumps)	$C_{\rm VDDC2}$	0.33	-	1	μF	2)	P_2.2.2	
Output Voltage including line regulation @ Active Mode/Stop Mode	V _{DDCOUT}	1.44	1.5	1.56	V	I _{load} < 40mA; with setting of VDDC output voltage to 1.5V in Stop Mode	P_2.2.3	
Load Regulation	V _{DDCLOR}	-50	-	50	mV	2 40mA; C = C _{VDDC1} +C _{VDDC2}	P_2.2.4	
Line Regulation	V _{DDCLIR}	-25	-	25	mV	V _s = 5.5 28V	P_2.2.5	
Over Voltage Detection	V _{DDCOV}	1.58	-	1.68	V	Overvoltage leads to SUPPLY_NMI	P_2.2.6	
Under Voltage Reset	V _{DDVUV}	1.10	-	1.19	V	-	P_2.2.7	
Over Current Diagnostic	I _{VDDCOC}	40	-	80	mA	-	P_2.2.8	

1) only min. value is tested.

2) Not subject to production test, specified by design.



28.2.4 VDDEXT Voltage Regulator 5.0V

Table 26 Electrical Characteristics

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)¹⁾

Parameter	Symbol		Value	S	Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
VDDEXT Regulator Active Mode	1				1		I
Specified Output Current	I _{VDDEXT}	0	-	20	mA	current flowing out of pin VDDEXT	P_2.3.1
Required decoupling capacitance	C _{VDDEXT1}	330	-	1000	nF	²⁾ ESR < 1 Ω	P_2.3.2
Required buffer capacitance for stability (load jumps)	C _{VDDEXT2}	100	-	1000	nF	3)	P_2.3.3
Output Voltage including line and load regulation	V _{DDEXT}	4.9	5.0	5.1	V	I _{load} < 20mA;Vs ≥ 5.5V	P_2.3.4
Output Drop	$V_{\rm s}$ - $V_{\rm DDEXT}$		50	+400	mV	$I_{\rm load}$ < 20mA; 3V < $V_{\rm s}$ < 5.0V	P_2.3.5
Load Regulation	V _{DDEXTLOR}	-80	-	20	mV	0.01 20mA; C = $C_{VDDEXT1}+C_{VDDEXT2};$ $V_{s} \ge 5.5V$	P_2.3.6
Line Regulation	V _{VDDEXTLIR}	-50	-	50	mV	V _s = 5.5 28V	P_2.3.7
Power Supply Ripple Rejection	P _{SSRVDDEXT}	50	-	-	dB	³⁾ V _s = 13.5V; f=0 1KHz; V _r =2Vpp; 0 20mA	P_2.3.8
Under Voltage Shutdown	V _{VDDEXTUV}	1.55	1.9	2.2	V	4)	P_2.3.9
Over Current Limitation	I _{VDDEXTOC}	100	250	380	mA	3)	P_2.3.10
VDDEXT output discharge resistance	R _{VDDEXT_DIS}	16	20	24	kΩ	-	P_2.3.11
VDDEXT Regulator Low Current	Mode						
Specified Output Current	$I_{\rm VDDEXT_LCM}$	0	-	5	mA	-	P_2.3.28
Output Voltage including line and oad regulation - Load 1	V _{DDEXT_LCM}	4.6	5.0	5.1	V	$I_{\text{load}} \le 5 \text{mA}; \text{Vs} \ge 5.5 \text{V}$	P_2.3.29
Output Drop - Load 1	V _s - V _{DDEXT_LCM}		50	+300	mV	$I_{load} \le 5mA;$ $3V < V_s \le 5V;$ C = $C_{VDDEXT1} + C_{VDDEXT2}$	P_2.3.30
Load Regulation - Load 1	V _{DDEXTLOR}	-250	-	250	mV	0 5mA; C = $C_{VDDEXT1}+C_{VDDEXT2};$ $V_s \ge 5.5V$	P_2.3.31
Line Regulation - Load 1	V _{VDDEXTLIR}	-300	-	300	mV	$I_{\text{load}} \le 5\text{mA};$ $V_{\text{s}} = 5.5 \dots 28\text{V}$	P_2.3.32
Power Supply Ripple Rejection	P _{SSRVDDEXT} _LCM	50	-	-	dB	³⁾ Vs= 13.5V; f=0 1KHz; Vr=2Vpp; 0 5mA	P_2.3.33



- 1) currents used in this table are positive but flowing out the pin VDDEXT
- 2) only min. value is tested.
- 3) Not subject to production test, specified by design.
- 4) When condition is met, the Bit VDDEXT_CTRL.VDDEXT_UV_IS will be set.



28.2.5 VPRE Voltage Regulator (PMU Subblock) Parameters

The PMU VPRE Regulator acts as a supply of VDDP and VDDC voltage regulators.

Table 27Functional Range

Parameter	Symbol		Values I		Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Specified Output Current	I _{VPRE}	-	-	90	mA	1)	P_2.4.1

1) Not subject to production test, specified by design.

28.2.5.1 Load Sharing of VPRE Regulator

The figure below shows the load sharing concept of VPRE regulator.



Figure 36 Load Sharing of VPRE Regulator



28.2.6 Power Down Voltage Regulator (PMU Subblock) Parameters

The PMU Power Down voltage regulator consists of two subblocks:

- Power Down Pre regulator: VDD5VPD
- Power Down Core regulator: VDD1V5_PD (Supply used for GPUDATAxy registers)

Both regulators are used as purely internal supplies. The following table contains all relevant parameter:

Table 28Functional Range

Parameter	Symbol	Values		Unit	Note / Test Condition	Number	
		Min.	Тур.	Max.			
Power-On Reset Threshold	$V_{\rm DD1V5_PD_}$ RSTTH	1.2	-	1.5	V	¹⁾ <i>I</i> _{load} = internal load connected to VDD1V5_PD	P_2.5.1

1) Not subject to production test, specified by design



28.3 System Clocks

28.3.1 Electrical Characteristics Oscillators and PLL

Table 29 Electrical Characteristics System Clocks

 $V_{\rm S}$ = 5.5 V to 28 V,, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Values	5	Unit	Note / Test Condition	Number	
		Min.	Тур.	Max.	-			
PMU Oscillators (Powe	r Manager	nent Unit						
Frequency of LP_CLK	$f_{\sf LP_CLK}$	17	20	23	MHz	this clock is used at startup and can be used in case the PLL fails	P_3.1.1	
Frequency of LP_CLK2	$f_{\rm LP_CLK2}$	70	100	130	kHz	this clock is used for cyclic wake	P_3.1.2	
CGU Oscillator (Clock	Generatio	n Unit Mic	rocontr	oller)				
Short term frequency deviation ¹⁾	f_{TRIMST}	-0.4%	_	+0.4%	MHz	within any 100 ms, e.g. after synchronization to a LIN frame (includes PLL accumulated jitter value).Assuption: T _j is varying < 30°C.	P_3.1.3	
Absolute accuracy	$f_{\sf TRIMABSA}$	-1.49%	-	+1.49%	MHz	Including temperature& lifetime drift and supply variation	P_3.1.4	
CGU-OSC Start-up time	t _{OSC}	-	-	10	μs	²⁾ startup time OSC from Sleep Mode, power supply stable	P_3.1.5	
PLL (Clock Generation	Unit Micro	ocontrolle	er) ²⁾	1				
VCO reference frequency range	f_{REF}	0.8	1	1.25	MHz		P_3.1.25	
VCO frequency (tuning) range	fvco	75	-	160	MHz		P_3.1.21	
Input frequency range	fosc	4	_	6	MHz	see also specified limits for $f_{\rm VCO}$ and $f_{\rm REF}$ resulting in restrictions for possible N divider settings	P_3.1.6	
XTAL1 input freq. range	foschp	4	-	6	MHz	see also specified limits for $f_{\rm VCO}$ and $f_{\rm REF}$ resulting in restrictions for possible N divider settings	P_3.1.23	
Output freq. range	f _{pll}	15	_	40	MHz	see also specified limits for $f_{\rm VCO}$ and $f_{\rm REF}$ resulting in restrictions for possible N divider settings	P_3.1.7	
Free-running frequency	$f_{\rm VCOfree}$	_	34	_	MHz		P_3.1.24	



Table 29 Electrical Characteristics System Clocks (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V,, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	s	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Input clock high/low time	t _{high/low}	10	-	-	ns		P_3.1.8
Peak period jitter	t _{jp}	-500	-	500	ps	for K=2; this parameter value is only valid with the combination of an external quartz oscillator (e.g. 5 MHz)	P_3.1.9
Accumulated jitter with external oscillator	jacc_ext	-	-	5	ns	for K=2; this parameter value is only valid with the combination of an external quartz oscillator (e.g. 5 MHz).	P_3.1.10
Lock-in time	tL	-	-	260	μs	this parameter represents the duration from module power-on to assertion of lock signal	P_3.1.11

1) The typical oscillator frequency is 40 MHz

2) Not subject to production test, specified by design.

28.3.2 External Clock Parameters XTAL1, XTAL2

Table 30Functional Range

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)¹⁾

Parameter	Symbol		Values		Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
Input voltage range limits for signal on XTAL1	V _{IX1_SR}	-1.7 + V _{DDC}	-	1.7	V	2)	P_3.2.1
Input voltage (amplitude) on XTAL1	V _{AX1_SR}	0.3 x V _{DDC}	-	-	V	³⁾ Peak-to-peak voltage	P_3.2.2
XTAL1 input current	I	-	-	±20	μA	$0 V < V_{IN} < V_{DDI}$	P_3.2.3
Oscillator frequency	fosc	4	-	6	MHz	Clock signal	P_3.2.4
Oscillator frequency	fosc	4	-	6	MHz	Crystal or Resonator	P_3.2.5
High time	t _{1_VCOBYP}	6	-	-	ns	4)5)	P_3.2.6
Low time	t _{2_VCOBYP}	6	-	-	ns	4)5)	P_3.2.7
Rise time	t _{3_VCOBYP}	-	8	8	ns	4)5)	P_3.2.8
Fall time	t _{4_VCOBYP}	-	8	8	ns	4)5)	P_3.2.9
High time	t _{1_PLLNM}	12	-	_	ns	5)6)	P_3.2.10



Table 30Functional Range (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)¹⁾

Parameter	Symbol	Symbol Values				Note /	Number
		Min.	Тур.	Max.		Test Condition	
Low time	t _{2_PLLNM}	12	-	-	ns	5)6)	P_3.2.11
Rise time	t _{3_PLLNM}	-	7	7	ns	5)6)	P_3.2.12
Fall time	t _{4_PLLNM}	-	7	7	ns	5)6)	P_3.2.13

1) Not subject to production test, specified by design.

2) Overload conditions must not occur on pin XTAL1.

3) The amplitude voltage V_{AX1} refers to the offset voltage V_{OFF} . This offset voltage must be stable during the operation and the resulting voltage peaks must remain within the limits defined by V_{IX1} .

4) this performance is only valid for Prescaler Mode (VCO Bypass mode).

5) tested with rectangular signal with $V_{IN_Low} = 0V$ to $V_{IN_High} = V_{DDC}$

6) this performance is only valid for PLL Normal Mode.



28.4 Flash Parameters

This chapter includes the parameters for the 64 KByte embedded flash module.

28.4.1 Flash Characteristics

Table 31 Flash Characteristics¹⁾

 $V_{\rm S}$ = 5.5 V to 28 V,, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Symbol		Values	6	Unit	Note /	Number
	Min.	Тур.	Max.		Test Condition	
t _{PR}	_	3 ²⁾	3.5	ms	$3V < V_{S} < 28V$	P_4.1.1
t _{ER}	_	4 ²⁾	4.5	ms	3V < V _S < 28V	P_4.1.2
t _{RET}	20	-	-	years	1,000 erase / program cycles	P_4.1.3
t _{RET}	50	-	-	years	1,000 erase / program cycles $T_{\rm j}$ = 30°C ³⁾	P_4.1.4
N_{ER}	30	-	-	kcycles	Data retention time 5 years	P_4.1.5
$N_{\rm SEC}$	10	-	-	cycles	Data retention time 20 years	P_4.1.6
$N_{\rm DD}$	32	-	-	kcycles	5)	P_4.1.7
	t_{PR} t_{ER} t_{RET} t_{RET} N_{ER} N_{SEC}	Min. t_{PR} - t_{ER} - t_{RET} 20 t_{RET} 50 N_{ER} 30 N_{SEC} 10	Min. Typ. t_{PR} - 3^{2}) t_{ER} - 4^{2}) t_{RET} 20 - t_{RET} 50 - N_{ER} 30 - N_{SEC} 10 -	Min. Typ. Max. t_{PR} - 3^{2}) 3.5 t_{ER} - 4^{2}) 4.5 t_{RET} 20 - - t_{RET} 50 - - N_{ER} 30 - - N_{SEC} 10 - -	Min. Typ. Max. t_{PR} - 3^{2} 3.5 ms t_{ER} - 4^{2} 4.5 ms t_{RET} 20 - - years t_{RET} 50 - - years N_{ER} 30 - - kcycles N_{SEC} 10 - - cycles	Min. Typ. Max. Test Condition t_{PR} - 3^{2}) 3.5 ms $3V < V_S < 28V$ t_{ER} - 4^{2}) 4.5 ms $3V < V_S < 28V$ t_{RET} 20 - - years $1,000 \text{ erase } /$ program cycles t_{RET} 50 - - years $1,000 \text{ erase } /$ program cycles t_{RET} 30 - - years $1,000 \text{ erase } /$ program cycles N_{ER} 30 - - kcycles Data retention time 5 years N_{SEC} 10 - - cycles Data retention time 20 years

1) Not subject for production test, specified by design.

2) Programming and erase times depend on the internal Flash clock source. The control state machine needs a few system clock cycles. The requirement is only relevant for extremely low system frequencies.

3) Derived by extrapolation of lifetime tests.

4) Temperature: 25 °C

5) This parameter limits the number of subsequent programming operations within a physical sector without a given page in this sector being (re-)programmed. The drain disturb limit is applicable if wordline erase is used repeatedly. For normal sector erase/program cycles this limit will not be violated. For data sectors the integrated EEPROM emulation firmware routines handle this limit automatically, for wordline erases in code sectors (without EEPROM emulation) it is recommended to execute a software based refresh, which may make use of the integrated random number generator NVMBRNG to statistically start a refresh.



28.5 Parallel Ports (GPIO)

28.5.1 Description of Keep and Force Current











TLE9844-2QX

Electrical Characteristics



Figure 39 Pull-Down Keep and Force Current

28.5.2 DC Parameters Port 0, Port 1, TMS, Reset

Table 32DC Characteristics Port0, Port1

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values				Note /	Number
		Min.	Тур.	Max.		Test Condition	
Input low voltage	V _{IL}	-0.3	-	0.3 x V _{DDP}	V	$^{1)} 4.5 V \le V_{DDP} \le 5.5 V$	P_5.2.1
Input low voltage	$V_{\rm IL_extend}$	-0.3	0.42 x V _{DDP}	-	V	$^{2)}$ 2.6V \leq V _{DDP} < 4.5V	P_5.2.14
Input high voltage	V _{IH}	0.7 x V _{DDP}	-	V _{DDP} + 0.3	V	$^{1)} 4.5 V \le V_{DDP} \le 5.5 V$	P_5.2.2
Input high voltage	$V_{\rm IH_extend}$	-	0.52 x V _{DDP}	V _{DDP} + 0.3	V	$^{2)}$ 2.6V \leq V _{DDP} < 4.5V	P_5.2.15
Input Hysteresis	HYS	0.11 x V _{DDP}	-	-	V	²⁾ 4.5V \leq V _{DDP} \leq 5.5V; Series resistance = 0 Ω	P_5.2.3
nput Hysteresis	HYS _{extend}	-	0.09 x V _{DDP}	-	V	$^{2)}$ 2.6V ≤ V _{DDP} < 4.5V; Series resistance = 0 Ω	P_5.2.16
Output low voltage	V _{OL}	-	-	1.0	V	$^{(3) 4)} I_{OL} \leq I_{OLmax}$	P_5.2.4
Output low voltage	V _{OL}	-	-	0.4	V	^{3) 5)} IOL ≤ IOLnom	P_5.2.5
Output high voltage	V _{OH}	V _{DDP} - 1.0	-	-	V	$^{(3) 4)} I_{OH} \ge I_{OHmax}$	P_5.2.6
Output high voltage	V _{OH}	V _{DDP} - 0.4	-	-	V	$^{(3)} S^{(5)} I_{OH} \geq I_{OHnom}$	P_5.2.7
Input leakage current	I _{OZ2}	-5	_	+5	μA	⁶⁾ $T_{\rm J} \le 85^{\circ}{\rm C}$, 0.45 V < $V_{\rm IN}$ < $V_{\rm DDP}$	P_5.2.8



P 5.2.13

Electrical Characteristics

Table 32 DC Characteristics Port0, Port1 (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
Input leakage current	I _{OZ2}	-15	-	+15	μA	$T_{\rm J} \le 150^{\circ}{\rm C},$ 0.45 V < $V_{\rm IN}$ < $V_{\rm DDP}$	P_5.2.9
Pull level keep current ⁷⁾	I _{PLK}	-	-	±200	μA	⁸⁾ $V_{\text{PIN}} \ge V_{\text{IH}}$ (up) $V_{\text{PIN}} \le V_{\text{IL}}$ (dn)	P_5.2.10
Pull level force current ⁷⁾	I _{PLF}	±1.5	-	_	mA	⁸⁾ $V_{\text{PIN}} \ge V_{\text{IL}}$ (up) $V_{\text{PIN}} \le V_{\text{IH}}$ (dn)	P_5.2.11
Pin capacitance	C _{IO}	-	_	10	pF	2)	P_5.2.12
Reset Pin Timing				-	k		-

Reset Pin Input Filter Time $T_{\text{filt}_{\text{RESET}}}$ –

1) Tested at V_{DDP} = 5V, specified for 2.55V < V_{DDP} < 5.1V.

- 2) Not subject to production test, specified by design.
- 3) The maximum deliverable output current of a port driver depends on the selected output driver mode. The limit for pin groups must be respected.

9)

μs

- 4) Tested at 2.55V < V_{DDP} < 5.1V, I_{OL} = 4mA, I_{OH} = -4mA, specified for 2.7V < V_{DDP} < 5.1V.
- 5) As a rule, with decreasing output current the output levels approach the respective supply level ($V_{OL} \rightarrow GND$, $V_{OH} \rightarrow V_{DDP}$). Tested at 2.55V < V_{DDP} < 5.1V, I_{OL} = 1mA, I_{OH} = -1mA.
- 6) The given values are worst-case values. In production test, this leakage current is only tested at 125°C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (*T*_J = junction temperature [°C]): *I*_{OZ} = 0.05 × e^(1.5 + 0.028×TJ) [µA]. For example, at a temperature of 95°C the resulting leakage current is 3.2 µA.

Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]):

 $I_{OZ} = I_{OZtempmax} - (1.6 \times DV) [\mu A]$

This voltage derating formula is an approximation which applies for maximum temperature.

7) Negative current is representing pullup; positive current is representing pulldown

8) Keep current: Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: V_{PIN} ≥ V_{IH} for a pull-up; V_{PIN} ≤ V_{IL} for a pull-down.
Force current: Drive the indicated minimum current through this pin to change the default pin level driven by the enabled.

Force current: Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{\text{PIN}} \leq V_{\text{IL}}$ for a pull-up; $V_{\text{PIN}} \geq V_{\text{IH}}$ for a pull-down.

These values apply to the fixed pull-devices in dedicated pins and to the user-selectable pull-devices in general purpose IO pins.

9) This filter time and its variation is derived from the time base $t_{LP CLK} = 1 / f_{LP CLK}$.

Note: Operating Conditions apply.

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current I_{OV} .

Port Output Driver Mode	Maximum Out (I _{OLmax} , - I _{OH}	· 、	Output Curren I _{OHnom})	Number	
	$\textbf{VDDP} \geq \textbf{4.5V}$	2.55V < VDDP < 4.5V	$\textbf{VDDP} \geq \textbf{4.5V}$	2.55V < VDDP < 4.5V	
Strong Driver	5 mA	3 mA	1.6 mA	1.0 mA	P_5.2.20

Table 33 Current Limits for Port Output Drivers¹⁾



Port Output Driver Mode	Maximum Out (I _{OLmax} , - I _{OH}	•	Output Curre I _{OHnom})	Number	
	$\textbf{VDDP} \geq \textbf{4.5V}$	2.55V < VDDP < 4.5V	$\textbf{VDDP} \geq \textbf{4.5V}$	2.55V < VDDP < 4.5V	
Medium Driver	3 mA	1.8 mA	1.0 mA	0.8 mA	P_5.2.21
Weak Driver	0.5 mA	0.3 mA	0.25 mA	0.15 mA	P_5.2.22

Table 33 Current Limits for Port Output Drivers¹ (cont'd)

1) Not subject to production test, specified by design.

28.5.3 DC Parameters Port 2

These parameters apply to the IO voltage range, 2.55 V $\leq V_{\text{DDP}} \leq$ 5.5 V.

Note: Operating Conditions apply.

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current I_{OV} .

Table 34 DC Characteristics Port 2

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values				Note /	Number
		Min.	Тур.	Max.		Test Condition	
Input low voltage	$V_{\rm IL_P2}$	-0.3	-	0.3 x V _{DDP}	V	$^{1)} 4.5V \le V_{DDP} \le 5.5V$	P_5.3.1
Input low voltage	V _{IL_P2_exte}	-0.3	0.42 x V _{DDP}	-	V	²⁾ 2.6V ≤ V _{DDP} < 4.5V	P_5.3.8
Input high voltage	V _{IH_P2}	0.7 x V _{DDP}	-	V _{DDP} + 0.3	V	$^{1)} 4.5V \le V_{DDP} \le 5.5V$	P_5.3.2
Input high voltage	$V_{\rm IH_P2_ext}$ end	-	0.52 x V _{DDP}	V _{DDP} + 0.3	V	²⁾ 2.6V ≤ V _{DDP} < 4.5V	P_5.3.9
Input Hysteresis	HYS _{P2}	0.11 x V _{DDP}	-	-	V	²⁾ 4.5V \leq V _{DDP} \leq 5.5V; Series resistance = 0 Ω	P_5.3.3
Input Hysteresis	HYS _{P2_ext}	-	0.09 x V _{DDP}	-	V	²⁾ 2.6V \leq V _{DDP} < 4.5V; Series resistance = 0 Ω	P_5.3.10
Input leakage current	I _{OZ1_P2}	-400	-	+400	nA	$\begin{array}{l} 4.5 \mathrm{V} \leq \mathrm{V}_{\mathrm{DDP}} \leq \\ 5.5 \mathrm{V} \\ T_{\mathrm{J}} \leq 85^{\circ} \mathrm{C}, \\ 0 \ \mathrm{V} < V_{\mathrm{IN}} < V_{\mathrm{DDP}} \end{array}$	P_5.3.4
Input leakage current (extended temperature range)	I _{OZ1_P2_T_} extend	-1	-	+1	uA	$2.6V \le V_{DDP} <$ 4.5V $T_{J} \le 150^{\circ}C,$ $0 V < V_{IN} < V_{DDP}$	P_5.3.11
Pull level keep current ⁴⁾	I _{PLK_P2}	-	-	±30	μA	$^{3)}$ VPIN ≥ VIH (up) VPIN ≤ VIL (dn)	P_5.3.5



Table 34 DC Characteristics Port 2 (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
Pull level force current ⁴⁾	I _{PLF_P2}	±750	-	-	μA	³⁾ VPIN ≤ VIL (up) VPIN ≥ VIH (dn)	P_5.3.6
Pin capacitance (digital inputs/outputs)	C_{IO_P2}	-	-	10	pF	2)	P_5.3.7

1) Tested at V_{DDP} = 5V, specified for 4.9V < V_{DDP} < 5.1V.

2) Not subject to production test, specified by design.

3) Keep current: Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{\text{PIN}} \ge V_{\text{IH}}$ for a pull-up; $V_{\text{PIN}} \le V_{\text{IL}}$ for a pull-down. Force current: Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{\text{PIN}} \le V_{\text{IL}}$ for a pull-up; $V_{\text{PIN}} \ge V_{\text{IH}}$ for a pull-down.

4) Negative current is representing pullup; positive current is representing pulldown

28.5.4 Operating Conditions

The following operating conditions must not be exceeded to ensure correct operation of the TLE9844-2QX. All parameters specified in the following sections refer to these operating conditions, unless otherwise noticed.

Note: Typical parameter values refer to room temperature and nominal supply voltage, minimum/maximum parameter values also include conditions of minimum/maximum temperature and minimum/maximum supply voltage. Additional details are described where applicable.

Table 35 Operating Condition Parameters

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	ol Values			Unit	Note /	Number	
		Min. Typ.		Max.		Test Condition		
Digital core supply voltage	V _{DDC}	1.35	_	1.6	V	Full active mode	P_5.4.1	
Digital supply voltage for IO pads	V_{DDP}	2.55	5.0	5.5	V	1)	P_5.4.2	
Digital ground voltage	V _{SS}	0	-	0	V	Reference voltage	P_5.4.3	
Overload current	I _{OV}	- 5.0	-	5.0	mA	Per IO pin ²⁾³⁾	P_5.4.4	
Overload current	I _{OV}	- 2.0	-	5.0	mA	Per analog input pin ²⁾³⁾	P_5.4.5	
Overload positive current coupling factor for analog inputs ⁴⁾	K _{OVA}	-	1.0 x 10 ⁻⁶	1.0 x 10 ⁻⁴	-	$I_{\rm OV} > 0^{3)}$	P_5.4.6	
Overload negative current coupling factor for analog inputs	K _{OVA}	-	2.5 x 10 ⁻⁴	1.5 x 10 ⁻³	-	$I_{\rm OV} < 0^{3)}$	P_5.4.7	
Overload positive current coupling factor for digital I/O pins	K _{OVD}	-	1.0 x 10 ⁻⁴	5.0 x 10 ⁻³	-	<i>I</i> _{OV} > 0 ³⁾	P_5.4.8	
Overload negative current coupling factor for digital I/O pins	K _{OVD}	-	1.0 x 10 ⁻²	3.0 x 10 ⁻²	-	<i>I</i> _{OV} < 0 ³⁾	P_5.4.9	
Absolute sum of overload currents	$\Sigma I_{OV} $	-	_	80	mA	3)	P_5.4.10	



1)Performance of pad drivers, A/D Converter, and Flash module depends on V_{DDP} .

If the external supply voltage V_{DDP} becomes lower than the specified operating range, a power reset must be generated. Otherwise, the core supply voltage V_{DDI} may rise above its specified operating range due to parasitic effects.

This power reset can be generated by the on-chip SWD. If the SWD is disabled the power reset must be generated by activating the PORST input

- 2) Overload conditions occur if the standard operating conditions are exceeded, i.e. the voltage on any pin exceeds the specified range: $V_{OV} > V_{IHmax}$ ($I_{OV} > 0$) or $V_{OV} < V_{ILmin}$ ($I_{OV} < 0$). The absolute sum of input overload currents on all pins may not exceed **50 mA**. The supply voltages must remain within the specified limits. Proper operation under overload conditions depends on the application.
 - Overload conditions must not occur on pin XTAL1 (powered by V_{DDIM}).
- Not subject to production test, specified by design.
- 4) An overload current (I_{OV}) through a pin injects an error current (I_{INJ}) into the adjacent pins. This error current adds to that pin's leakage current (I_{OZ}) . The value of the error current depends on the overload current and is defined by the overload coupling factor K_{OV} . The polarity of the injected error current is reversed from the polarity of the overload current that produces it.

The total current through a pin is $|I_{TOT}| = |I_{OZ}| + (|I_{OV}| \times K_{OV})$. The additional error current may distort the input voltage on analog inputs.


28.6 LIN Transceiver

28.6.1 Electrical Characteristics

Table 36 Electrical Characteristics LIN Transceiver

Parameter	Symbol		Values		Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Bus Receiver Interface			ľ				
Receiver threshold voltage, recessive to dominant edge	$V_{\mathrm{th_dom}}$	0.4 ×V _s	0.45 ×V _S	0.53 x V _S	V	SAE J2602	P_6.1.1
Receiver dominant state	$V_{\rm BUSdom}$	-27	-	0.4 ×V _S	V	LIN Spec 2.2 (Par. 17)	P_6.1.2
Receiver threshold voltage, dominant to recessive edge	$V_{\mathrm{th_rec}}$	0.47 x V _S	0.55 ×V _S	0.6 ×V _S	V	SAE J2602	P_6.1.3
Receiver recessive state	V _{BUSrec}	$0.6 \times V_{\rm S}$	_	1.15 ×V _s	V	¹⁾ LIN Spec 2.2 (Par. 18)	P_6.1.4
Receiver center voltage	$V_{\rm BUS_CN}$ t	0.475 × V _S	0.5 ×V _S	0.525 × V _S	V	²⁾ LIN Spec 2.2 (Par. 19)	P_6.1.5
Receiver hysteresis	V _{HYS}	0.07 × V _S	0.12 ×V _S	0.175 × V _S	V	³⁾ LIN Spec 2.2 (Par. 20)	P_6.1.6
Wake-up threshold voltage	$V_{\rm BUS,wk}$	$0.4 \times V_{S}$	$0.5 \times V_{\rm S}$	0.6 ×V _S	V	-	P_6.1.7
Dominant time for bus wake- up	t _{WK,bus}	30	_	150	μs	including analog and digital filter time. Digital filter time can be adjusted by PMU.CNF_WAKE_FIL TER	P_6.1.8
Bus Transmitter Interface							
Bus recessive output voltage	$V_{\rm BUS,ro}$	0.8 ×V _S	-	Vs	V	V_{TxD} = high Level	P_6.1.9
Bus short circuit current	I _{BUS,sc}	40	100	150	mA	Current Limitation for driver dominant state driver on V_{BUS} = 18 V; LIN Spec 2.2 (Par. 12)	P_6.1.1(
Leakage current	I _{BUS_NO_} gnd	-1000	-450	0	μA	$V_{\rm S}$ = 0 V; $V_{\rm BUS}$ = -12 V; LIN Spec 2.2 (Par. 15)	P_6.1.11
Leakage current	I _{BUS_NO_} bat	-	10	20	μA	$V_{\rm S}$ = 0 V; $V_{\rm BUS}$ = 18 V; LIN Spec 2.2 (Par. 16)	P_6.1.12
Leakage current	I _{BUS_PAS} _dom	-1	-	-	mA	$V_{\rm S}$ = 18 V; $V_{\rm BUS}$ = 0 V; LIN Spec 2.2 (Par. 13)	P_6.1.13
Leakage current	I _{BUS_PAS}	-	_	20	μA	$V_{\rm S}$ = 8 V; $V_{\rm BUS}$ = 18 V; LIN Spec 2.2 (Par. 14)	P_6.1.14



Table 36 Electrical Characteristics LIN Transceiver (cont'd)

 $V_{\rm s}$ = 5.5V to 18V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	es	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Bus pull-up resistance	R _{BUS}	20	30	47	kΩ	Normal mode LIN Spec 2.2 (Par. 26), also present in Sleep mode	P_6.1.15
AC Characteristics - Trans	ceiver No	rmal SI	ope Mode)			
Propagation delay bus dominant to RxD LOW	$t_{\rm d(L),R}$	0.1	1	6	μs	LIN Spec 2.2 (Param. 31)	P_6.1.16
Propagation delay bus recessive to RxD HIGH	t _{d(H),R}	0.1	1	6	μs	LIN Spec 2.2 (Param. 31)	P_6.1.17
Receiver delay symmetry	t _{sym,R}	-2	-	2	μs	$t_{\text{sym,R}} = t_{d(L),R} - t_{d(H),R};$ LIN Spec 2.2 (Par. 32)	P_6.1.18
Duty cycle D1 Normal Slope Mode (for worst case at 20 kbit/s)	t _{duty1}	0.396	-	_		⁴⁾ duty cycle 1 $TH_{Rec}(max) =$ $0.744 \times V_S;$ $TH_{Dom}(max) =$ $0.581 \times V_S;$ $t_{bit} = 50 \ \mu s;$ $D1 = t_{bus_rec(min)} / 2 \times t_{bit};$ LIN Spec 2.2 (Par. 27)	P_6.1.19
Duty cycle D2 Normal Slope Mode (for worst case at 20 kbit/s)	t _{duty2}	_	-	0.581		⁴⁾ duty cycle 2 $TH_{Rec}(min) = 0.422 \times V_{S};$ $TH_{Dom}(min) =$ $0.284 \times V_{S};$ $t_{bit} = 50 \ \mu s;$ $D2 = t_{bus_rec(max)} / 2 \times t_{bit};$ LIN Spec 2.2 (Par. 28)	P_6.1.20
AC Characteristics - Trans	ceiver Lo	w Slope	Mode	I	I		1
Propagation delay bus dominant to RxD LOW	$t_{d(L),R}$	0.1	1	6	μs	LIN Spec 2.2 (Param. 31)	P_6.1.21
Propagation delay bus recessive to RxD HIGH	t _{d(H),R}	0.1	1	6	μs	LIN Spec 2.2 (Param. 31)	P_6.1.22

Receiver delay symmetry

P_6.1.23

 $t_{\text{sym,R}} = t_{d(L),R} - t_{d(H),R};$ LIN Spec 2.2 (Par. 32)

2

μs

-2

_

t_{sym,R}



Table 36 Electrical Characteristics LIN Transceiver (cont'd)

Parameter	Symbol		Value	es	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Duty cycle D3 (for worst case at 10,4 kbit/s)	t _{duty1}	0.417	_	-		⁴⁾ duty cycle 3 $TH_{Rec}(max) =$ $0.778 \times V_S;$ $TH_{Dom}(max) =$ $0.616 \times V_S;$ $t_{bit} = 96 \ \mu s;$ $D3 = t_{bus_rec(min)} / 2 \times t_{bit};$ LIN Spec 2.2 (Par. 29)	P_6.1.24
Duty cycle D4 (for worst case at 10,4 kbit/s)	t _{duty2}	-	-	0.590		⁴⁾ duty cycle 4 $TH_{Rec}(min) = 0.389 \times V_{S};$ $TH_{Dom}(min) =$ $0.251 \times V_{S};$ $t_{bit} = 96 \ \mu s;$ $D4 = t_{bus_rec(max)} / 2 \times t_{bit};$ LIN Spec 2.2 (Par. 30)	P_6.1.25
AC Characteristics - Trans	ceiver Fa	st Slope	Mode				
Propagation delay bus dominant to RxD LOW	$t_{d(L),R}$	0.1	1	6	μs	-	P_6.1.26
Propagation delay bus recessive to RxD HIGH	t _{d(H),R}	0.1	1	6	μs	-	P_6.1.27
Receiver delay symmetry- extended supply voltage range	t _{sym,R}	-2.0	-	2.0	μs	$t_{\rm sym,R} = t_{\rm d(L),R} - t_{\rm d(H),R};$	P_6.1.42
Duty cycle D5 (used for 62,5 kbit/s)	t _{duty1}	0.395	-	-		⁴⁾ duty cycle 5 $TH_{Rec}(max) =$ $0.744 \times V_S;$ $TH_{Dom}(max) =$ $0.581 \times V_S;$ $t_{bit} = 16\mu s;$ $D5 = t_{bus_rec(min)} / 2 \times t_{bit};$	P_6.1.29
Duty cycle D6 (used for 62,5 kbit/s)	t _{duty2}	-	-	0.581		⁴⁾ duty cycle 6 TH _{Rec} (min)= 0.422 × $V_{\rm S}$; TH _{Dom} (min)= 0.284 × $V_{\rm S}$; $t_{\rm bit}$ = 16 µs; D6 = $t_{\rm bus_rec(max)}$ / 2 x $t_{\rm bit}$;	P_6.1.30
AC Characteristics - Flash	Mode	+	 				•
Propagation delay	$t_{d(L),R}$	0.1	0.5	6	μs	-	P_6.1.31



Table 36 Electrical Characteristics LIN Transceiver (cont'd)

 $V_{\rm s}$ = 5.5V to 18V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	es	Unit	Note / Test Condition	Number	
		Min.	Тур.	Max.				
Duty cycle D7 (for worst case at 115 kbit/s) for +1 µs Receiver delay symmetry (used for 250 kbit/s programming)	t _{duty1}	0.395	-	_		⁵⁾ duty cycle D7 $TH_{Rec}(max) =$ $0.744 \times V_S;$ $TH_{Dom}(max) =$ $0.581 \times V_S; t_{bit} = 8.7 \ \mu s;$ $D7 = t_{bus_rec(min)} / 2 \times t_{bit};$	P_6.1.34	
Duty cycle D8 (for worst case at 115 kbit/s) for +1 µs Receiver delay symmetry (used for 250 kbit/s programming)	t _{duty2}	-	-	0.578		⁵⁾ duty cycle D8 TH _{Rec} (min) = 0.422 × $V_{\rm S}$; TH _{Dom} (min) = 0.284 × $V_{\rm S}$; $t_{\rm bit}$ = 8.7 µs; D8 = $t_{\rm bus_rec(max)}$ / 2 × $t_{\rm bit}$;	P_6.1.35	
LIN input capacity	$C_{\text{LIN}_{\text{IN}}}$	_	15	30	pF	6)	P_6.1.36	
TxD dominant time out	t _{timeout}	6	12	20	ms	$V_{\text{TxD}} = 0 \text{ V}$	P_6.1.37	
Thermal Shutdown (Junction	on Tempe	erature)			l			

Thermal shutdown temp.	$T_{\rm jSD}$	160	180	200	°C	6)	P_6.1.38
Thermal shutdown hyst.	ΔT	_	10	_	К	6)	P_6.1.39

1) Maximum limit specified by design.

2) $V_{\text{BUS}_\text{CNT}} = (V_{\text{th}_\text{dom}} + V_{\text{th}\,\text{rec}})/2$

3) $V_{\rm HYS} = V_{\rm BUSrec} - V_{\rm BUSdom}$

4) Bus load concerning LIN Spec 2.2: Load 1 = 1 nF / 1 k Ω = C_{BUS} / R_{BUS} Load 2 = 6.8 nF / 660 Ω = C_{BUS} / R_{BUS} Load 3 = 10 nF / 500 Ω = C_{BUS} / R_{BUS}

5) Bus load

Load 1 = 1 nF / 500 Ω = $C_{\rm BUS}$ / $R_{\rm BUS}$



28.7 High-Speed Synchronous Serial Interface

28.7.1 SSC Timing

The table below provides the SSC timing in the TLE9844-2QX.

Table 37 SSC Master Mode Timing (Operating Conditions apply; CL = 50 pF)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Values		Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
SCLK clock period	t ₀	¹⁾ 2 * T _{SSC}	-	_		$^{2)} V_{\rm DDP}$ > 2.7 V	P_7.1.1
MTSR delay from SCLK	t ₁	10	-	_	ns	²⁾ $V_{\rm DDP}$ > 2.7 V	P_7.1.2
MRST setup to SCLK	t ₂	10	-	_	ns	²⁾ $V_{\rm DDP}$ > 2.7 V	P_7.1.3
MRST hold from SCLK	t ₃	15	-	_	ns	²⁾ $V_{\rm DDP}$ > 2.7 V	P_7.1.4

1) $T_{SSCmin} = T_{CPU} = 1/f_{CPU}$. If $f_{CPU} = 20$ MHz, $t_0 = 100$ ns. T_{CPU} is the CPU clock period.



Figure 40 SSC Master Mode Timing



28.8 Measurement Unit

28.8.1 Electrical Characteristics

Table 38 Supply Voltage Signal Conditioning

Parameter	Symbol		Values		Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
ADC1 - Battery / Supply V	/oltage Measure	ement	V_{BAT_SE}	INSE / V	s		
Input to output voltage attenuation: V _{BAT_SENSE} / V _S	ATT_{VBAT_SENSE} , ATT_{VS}	_	0.047	-			P_8.1.10
Nominal operating input voltage range $V_{\rm BAT_SENSE} / V_{\rm S}$	$V_{\rm BAT_SENSE,}$ range, $V_{\rm S,\ range}$	0	_	25.7 7	V	²⁾ Max. value corresponds to typ. ADC full scale input;	P_8.1.11
Accuracy of $V_{\text{BAT}_{\text{SENSE}}} / V_{\text{S}}$ after calibration - with IIR filter	$\Delta V_{\rm BAT_SENSE_II}$ r, $V_{\rm S_IIR}$	-200	-	200	mV	V_{s} = 5.5V to 18V, T_{j} = -40125°C, $f_{ADCI} = f_{sys_max}$ ADC1_FILTCOEFF0_11. CHx = 11'b.	P_8.1.12
Accuracy of $V_{\rm BAT_SENSE} / V_{\rm S}$ after calibration	$\frac{\Delta V_{\text{BAT}_\text{SENSE}}}{V_{\text{S}}},$	-300	-	300	mV	V_{s} = 5.5V to 18V, T_{j} = -40125°C, $f_{ADCI} = f_{sys_max}$.	P_8.1.36
ADC1 - Monitoring Input	Voltage Measur	ement	V_{MONx}				
Input to output voltage attenuation: VMONx	ATT _{VMONx}	-	0.039	-			P_8.1.13
Nominal operating input voltage range VMONx	$V_{\mathrm{MONx,range}}$	0	-	31.0 5	V	²⁾ Max. value corresponds to typ. ADC full scale input;	P_8.1.14
Accuracy of $V_{\rm MONx}$ sense after calibration - with IIR filter	$\Delta V_{MONx_{IIR}}$	-241	-	241	mV	V_{s} = 5.5V to 18V, T_{j} = -40125°C, $f_{ADCI} = f_{sys_max}$ ADC1_FILTCOEFF0_11. CHx = 11'b.	P_8.1.33
Accuracy of V_{MONx} sense after calibration - Reduced Operating Range - with IIR filter	$\Delta V_{MONx_ROR_IIR}$	-170	-	170	mV	²⁾ V_{s} = 5.5V to 18V, T_{j} = -40125°C, $V_{MONx,range}$ = 0V to 12V, $f_{ADCI} = f_{sys_max}$, ADC1_FILTCOEFF0_11. CHx = 11'b.	P_8.1.20



Table 38Supply Voltage Signal Conditioning (cont'd)

Parameter	Symbol		Values		Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Accuracy of V_{MONx} sense after calibration	ΔV_{MONx}	-361	-	361	mV	²⁾ V_{s} = 5.5V to 18V, T_{j} = -40125°C, $f_{ADCI} = f_{sys_max}$.	P_8.1.37
ADC1 - Port 2.x Voltage I	Veasurement	V _{2.x}			*	· · · · ·	
Input to output voltage attenuation: VPort2.x	ATT _{2.x}	-	0.219	-		_	P_8.1.15
Nominal operating input voltage range VPort2.x	$V_{ m Port2.x,range}$	0	_	5.53 1)	V	²⁾ Max. value corresponds to typ. ADC full scale input;	P_8.1.16
Accuracy of $V_{\text{Port2.x}}$ sense after calibration - with IIR filter	$\Delta V_{Port2.x_IIR}$	-43	_	43	mV	V_{s} = 5.5V to 18V, T_{j} = -40125°C, $f_{ADCI} = f_{sys_{max}}$ ADC1_FILTCOEFF0_11. CHx = 11'b.	P_8.1.34
Accuracy of $V_{\text{Port2.x}}$ sense after calibration	$\Delta V_{\text{Port2.x}}$	-67	-	67	mV	V_{s} = 5.5V to 18V, T_{j} = -40125°C, $f_{ADCI} = f_{sys_max}$.	P_8.1.38
ADC2 - Supply Voltage N	leasurement V	/s					
Input to output voltage attenuation: $V_{\rm S}$	ATT_{VS_ADC2}	-	0.039	-			P_8.1.1
Nominal operating input voltage range V _S	V _{S,ADC2}	3	-	31.0 5	V	²⁾ Max. value corresponds to typ. ADC full scale input; $3V < V_S < 28V$	P_8.1.2
Accuracy of $V_{\rm S}$ after calibration	$\Delta V_{\rm S,ADC2}$	-270	-	270	mV	V _s = 5.5V to 18V, T _j = -40125°C	P_8.1.3
ADC2 - VDDEXT Voltage	Measurement	V _{DDEXT}					
Input to output voltage attenuation: VDDEXT	ATT _{VDDEXT}	-	0.203	-		_	P_8.1.17
Nominal operating input voltage range VDDEXT	$V_{\rm DDEXT,range}$	0	-	5.96	V	²⁾ Max. value corresponds to typ. ADC full scale input;	P_8.1.18
ADC2 - Pad Supply Volta	ge Measurem	ent V_{VD}	DP		·	·	·
Input-to-output voltage attenuation: VDDP	ATT _{VDDP}	-	0.203	-		_	P_8.1.4
							ļ



Table 38 Supply Voltage Signal Conditioning (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Values	5	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.	1		
ADC2 - Reference Voltag	ge Measureme	ent $V_{\rm BG}$					1
Input-to-output voltage attenuation: VBG	ATT _{VBG}	-	0.75	-		_	P_8.1.6
Nominal operating input voltage range VBG	$V_{\rm BG,range}$	0.8	-	VDD C - 0.1V	V	²⁾ Max. value corresponds to typ. ADC full scale input;	P_8.1.7
Value of ADC2- <i>V</i> _{BG} measurement after calibration	V _{BG_PMU}	0.90	1.0	1.1	V	_	P_8.1.39
ADC2 - Core supply Volt	age Measurer	ment $V_{\rm D}$	DC			•	
Input-to-output voltage attenuation: VDDC	ATT _{VDDC}	-	0.75	_		-	P_8.1.8
Nominal operating input voltage range VDDC	$V_{ m DDC,range}$	0.6	-	VDD C + 0.1V	V	²⁾ Max. value corresponds to typ. ADC full scale input;	P_8.1.9

1) This typical theoretical full scale is not reached as the internal ESD Clamping Structure limits the voltage to max. 5.2V.



28.8.2 Central Temperature Sensor Module

28.8.2.1 Electrical Characteristics

Table 39 Electrical Characteristics Temperature Sensor Module

 $V_{\rm S}$ = 5.5 V to 28 V, , $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values L		Unit	Note / Test Condition	Number	
		Min.	Тур.	Max.			
Output voltage V _{TEMP} at $T_0=0^{\circ}C (273 \text{ K})^{2)}$	а	-	0.628	-	V	T ₀ =0°C (273 K)	P_8.2.1
Temperature sensitivity b ²⁾	b	-	2.31	_	mV/K		P_8.2.2
Accuracy_1	Acc_1	-10	-	10	°C	¹⁾ -40°C < $T_{\rm j}$ < 85°C	P_8.2.3
Accuracy_2	Acc_2	-15	-	15	°C	125°C < <i>T</i> _j < 175°C	P_8.2.4
Accuracy_3	Acc_3	-5	-	5	°C	²⁾ 85°C < $T_{\rm j}$ < 125°C	P_8.2.5

1) Accuracy with reference to on-chip temperature calibration measurement.



28.9 ADC1 (10-Bit)

28.9.1 ADC1 Reference Voltage

Table 40DC Specifications

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Reference Voltage	V_{BG}	-1%	1.211	+1%	V		P_9.1.10
Temperature Drift	$\Delta V_{\rm BG}$	-1%		+1%	V		P_9.1.11

28.9.2 Electrical Characteristics ADC1 (10-Bit)

These parameters describe the conditions for optimum ADC performance.

Note: Operating Conditions apply.

Table 41 A/D Converter Characteristics

Parameter	Symbol		Value	s	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Analog clock frequency	$f_{\sf ADCI}$	5	_	40	MHz	1)	P_9.2.1
DNL error	EA _{DNL}	_	_	± 2	LSB	2)	P_9.2.8
INL error	EA _{INL}	-	_	± 3	LSB	-	P_9.2.9
Gain error	EA _{GAIN}	-	-	± 1.2	% of FSR 3)	⁴⁾ calibrated; Gain Error is calibrated by implemented calibration unit	P_9.2.10
Offset error	EA _{OFF}	-	-	± 2.5	LSB	⁴⁾ calibrated; Offset Error is calibrated by implemented calibration unit	P_9.2.11
Total unadjusted error	EA _{TUE}	-	-	± 10	LSB	already calibrated	P_9.2.33



Table 41 A/D Converter Characteristics (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, , $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	s	Unit	Note /	Number
		Min.	Тур.	Max.		Test Condition	
Input referred noise	V _{Noise_LSB}	-	-	1.5	LSB rms	$^{4)}T_{j}$ = 25°C; this value is determined out of 4 consecutive measurements which are averaged.	P_9.2.34
Cross-coupling Attenuation between LV Channels	EA _{CCOUP}	_	±1	± 2	LSB	4)	P_9.2.12
Input capacitance of a HV analog input	C_{AINT_HVI}	-	-	200	fF	4)	P_9.2.13
Input capacitance of a LV analog input	C_{AINT_LVI}	-	-	200	fF	4)	P_9.2.19

1) The limit values for f_{ADCI} must not be exceeded when selecting the peripheral frequency and the prescaler setting.

2) this parameter is measured with disabled hardware calibration

3) this Gain error is calibrated by IFX end of line

4) Not subject to production test



28.10 High-Voltage Monitoring Input

28.10.1 Electrical Characteristics

Table 42 Electrical Characteristics Monitoring Input

 $V_{\rm S}$ = 5.5 V to 28 V; $T_{\rm j}$ = -40 °C to +150 °C; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Values		Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
MON Input Pin charac	teristics			1			
Wake-up/monitoring threshold voltage	V _{MONth}	0.4*V _s	0.5*V _s	0.6*V _s	V	without external serial resistor R_s (with R_s :DV = $I_{PD/PU} * R_s$);	P_10.1.1
Threshold hysteresis	$V_{\rm MONth,hys}$	0.015* V _s	0.06*V _s	0.10*V _s	V	in all modes; without external serial resistor R_s (with R_s :dV = $I_{PD/PU}$ * R_s); 5.5 V < V_s < 18 V	P_10.1.2
Threshold hysteresis- extended supply voltage range	$V_{\rm MONth, hys}$ _VS_extende d	0.02*V _s	0.06*V _s	0.12*V _s	V	in all modes; without external serial resistor R_s (with R_s :dV = $I_{PD/PU}$ * R_s); 18 V < V_S < 28 V	P_10.1.7
Pull-up current	$I_{\rm PU, MON}$	-20	-10	-5	μA	0.6*V _s ;	P_10.1.3
Pull-down current	$I_{\rm PD,\;MON}$	5	10	20	μA	0.4*V _s ;	P_10.1.4
Input leakage current	$I_{\rm LK,MON}$	-2	-	2	μA	0 V < V _{MON_IN} < 28 V	P_10.1.5
Timing							
Wake-up filter time	t _{FT,MON}	-	20	-	μs	1)	P_10.1.6

1) With pull-up, pull down current disabled.



28.11 High Side Switches

28.11.1 Electrical Characteristics

Table 43Electrical Characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
PWM frequency of HS with Slew Rate Control	f _{pwm_w_sr}	0	-	10	kHz	¹⁾ Frequency must be configured in the PWM Generator	P_11.1.1
PWM frequency of HS without Slew Rate Control	f_{PWM} _w/o_sr	0	-	25 ²⁾	kHz	¹⁾ Frequency must be configured in the PWM Generator	P_11.1.2
Output HS							
ON-State Resistance	R _{ON}	2	10	18	Ω	5.5 V < $V_{\rm S}$ < 28V, Ids=100mA, $T_{\rm j}$ = 25 °C	P_11.1.3
Output leakage Current	I _{leakage}	_	-	2	μA	Output OFF 0 V < V_{XLO} < V_S ; $T_j \le 150 \text{ °C}$	P_11.1.4
Output Slew Rate (rising) with slow Slew Rate setting (Slew Rate 1)	SR _{raise_SR1}	1	-	10	V/µs	20% to 80% of $V_{\rm S}$ $V_{\rm S}$ = 9 to 18V $R_{\rm L}$ =300 $\Omega^{1)}$	P_11.1.5
Output Slew Rate (falling) with slow Slew Rate setting (Slew Rate 1)	SR_{fall_SR1}	-10	-	-1	V/µs	80% to 20% of $V_{\rm S}$ $V_{\rm S}$ = 9 to 18V $R_{\rm L}$ =300 $\Omega^{1)}$	P_11.1.6
Output Slew Rate (rising) with fast Slew Rate setting (Slew Rate 2)	SR _{raise_SR2}	18.0	-	55.0	V/µs	20% to 80% of $V_{\rm S}$ $V_{\rm S}$ = 9 to 18V $R_{\rm L}$ =300 $\Omega^{1)}$	P_11.1.7
Output Slew Rate (falling) with fast Slew Rate setting (Slew Rate 2)	SR _{fall_SR2}	-43.4	-	-12.5	V/µs	80% to 20% of $V_{\rm S}$ $V_{\rm S}$ = 9 to 18V $R_{\rm L}$ =300 $\Omega^{1)}$	P_11.1.8
Turn ON Delay time (Slew Rate 1)	t _{IN-HS_SR1}	-	-	4.5	μs	ON = 1 to 20% of $V_{\rm S}$ $R_{\rm L}$ =300 Ω	P_11.1.9
Turn ON time (Slew Rate 1)	t _{ON_SR1}	1	-	15	μs	$V_{\rm S}$ = 9 to 18V HS_ON=1 to 80% of $V_{\rm S}$ $R_{\rm L}$ =300 Ω $T_{\rm j}$ =25°C	P_11.1.10
Turn OFF time (Slew Rate 1)	t _{OFF_SR1}	1	-	15	μs	$V_{\rm S}$ = 9 to 18V HS_ON= 0 to 20% of $V_{\rm S}$ $R_{\rm L}$ =300 Ω ; $T_{\rm j}$ =25°C	P_11.1.11



Table 43 Electrical Characteristics (cont'd)

Parameter	Symbol		Values	5	Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
Turn ON Delay time (Slew Rate 2)	t _{IN-HS_SR2}	-	-	1	μs	ON = 1 to 20% of $V_{\rm S}$ $R_{\rm L}$ =300 Ω	P_11.1.55
Turn ON time (Slew Rate 2)	t _{ON_SR2}	-	-	3	μs	$V_{\rm S}$ = 9 to 18V HS_ON=1 to 80% of $V_{\rm S}$ $R_{\rm L}$ =300 Ω $T_{\rm j}$ =25°C	P_11.1.56
Turn OFF time (Slew Rate 2)	t _{OFF_SR2}	-	-	3	μs	$V_{\rm S}$ = 9 to 18V HS_ON= 0 to 20% of $V_{\rm S}$ $R_{\rm L}$ =300 Ω ; $T_{\rm j}$ =25°C	P_11.1.57
Over-current detection		·			·		·
Overcurrent threshold 0	I _{octh0}	26	42	60	mA	V _S = 13.5V HSx_OC_SEL =00	P_11.1.12
Overcurrent threshold 0 hysteresis	I _{octh0,hyst}	-	14	-	mA	¹⁾ HSx_OC_SEL =00	P_11.1.13
Overcurrent threshold 1	I _{octh1}	51	60	80	mA	V _S = 13.5V HSx_OC_SEL =01	P_11.1.14
Overcurrent threshold 1 hysteresis	I _{octh1,hyst}	-	17	-	mA	¹⁾ HSx_OC_SEL =01	P_11.1.15
Overcurrent threshold 2	I _{octh2}	101	123	150	mA	V _S = 13.5V HSx_OC_SEL =10	P_11.1.16
Overcurrent threshold 2 hysteresis	I _{octh2,hyst}	-	25	-	mA	¹⁾ HSx_OC_SEL =10	P_11.1.17
Overcurrent threshold 3	I _{octh3}	151	176	210	mA	V _S = 13.5V HSx_OC_SEL =11	P_11.1.18
Overcurrent threshold 3 hysteresis	I _{octh3,hyst}	-	30	-	mA	¹⁾ HSx_OC_SEL =11	P_11.1.19
Over-current shutdown response time	t _{ocft}	8	-	80	μs	¹⁾ VS = 13.5V, $R_{\rm L}$ =100 Ω , HS_ON to OC_SD (including switch- on time)	P_11.1.20
ON-state open load detection	'n					1	
Open load threshold	$I_{\rm OLONth}$	0.46	1.32	2.2	mA	-	P_11.1.21
Hysteresis	$I_{\rm OLONhys}$	35	155	300	μA	_	P_11.1.22
Cyclic sense mode							
Current capability	I _{HS max}	40	-	-	mA	Sleep Mode / Stop Mode	P_11.1.23
ON-State Resistance	R _{ON,static}	_	-	40	Ω	lds = 40mA,	P_11.1.24



Table 43 Electrical Characteristics (cont'd)

 $V_{\rm S}$ = 5.5 V to 28 V, $T_{\rm j}$ = -40 °C to +150 °C, all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

Parameter	Symbol		Value	S	Unit	Note / Test Condition	Number	
		Min.	Тур.	Max.				
Output Slew Rate (rising)	SR _{rise_cyc}	1	-	-	V/µs	20% to 80% of $V_{\rm S}$ $V_{\rm S}$ = 9 to 18V $R_{\rm L}$ =300 Ω	P_11.1.25	
Output Slew Rate (falling)	SR _{fal_cycl}	-	-	-1	V/µs	80% to 20% of $V_{\rm S}$ V _S = 9 to 18V $R_{\rm L}$ =300Ω	P_11.1.26	
Delay Time CYCLIC_ON-HS	t _{IN_cyc}	-	-	2	μs	ON =1 to 20% of $V_{\rm S}$ RL=300 Ω	P_11.1.27	
Turn-ON time	t _{ON_cyc}	-	-	15	μs	$V_{\rm S}$ = 9 to 18V ON=1 to 80% $R_{\rm L}$ =300Ω	P_11.1.28	
Turn-OFF time	t _{OFF_cyc}	-	-	15	μs	$V_{\rm S}$ = 9 to 18V ON=0 to 20% of $V_{\rm S}$ $R_{\rm L}$ =300Ω; $T_{\rm j}$ =25°C	P_11.1.29	

1) Not subject to production test, specified by design.

2) this is an additional requirement which refers to a 470hm series resistor to charge an external power mos gate.



28.12 Low Side Switches

28.12.1 Electrical Characteristics

Table 44 Electrical Characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Тур.	Max.			
PWM Frequency of LS	$f_{\rm PWM}$	-	-	25	kHz	$^{1)}R_{L}$ =270 Ω	P_12.1.1
Overcurrent Limitation	$I_{\rm LSTyp}$	270	300	330	mA		P_12.1.2
ON-State Resistance	R _{ON}	1	4	10	Ω	I _{ds} =100mA;	P_12.1.3
Leakage Current	I_{leakage}	-	-	2	μA	$0 V < V_{LS} < V_{S};$ $T_{j} < 85^{\circ}C$	P_12.1.5
Turn ON Delay time, slow mode	t _{dOn-LS}	-	-	50	μs	²⁾ LS_ON=1 to 0.9*Vs $V_{\rm S}$ =13.5V, $R_{\rm L}$ =270Ω	P_12.1.6
Turn ON Delay time, PWM mode	t _{dOn,f-LS}	-	-	0.5	μs	LS_ON=1 to 0.9*Vs $V_{\rm S}$ =13.5V, $R_{\rm L}$ =270 Ω	P_12.1.7
Turn ON fall time, PWM mode	t _{ONF,PWM}	-	1	1.25	μs	$V_{\rm LS}$ 0.9*Vs to 0.1*Vs $V_{\rm S}$ =13.5V, $R_{\rm L}$ =270Ω	P_12.1.8
Turn ON fall time, slow mode	t _{ONF,Slow}	-	100	150	μs	²⁾ VLS 0.9*Vs to 0.1*Vs VS=13.5V, RL =270Ω	P_12.1.9
Turn OFF Delay time, slow mode	t _{dOff-LS}	-	-	50	μs	²⁾ LS_ON=0 to 0.1*Vs $V_{\rm S}$ =13.5V, $R_{\rm L}$ =270Ω	P_12.1.10
Turn OFF Delay time, PWM mode	t _{dOff,f-LS}	-	-	2	μs	LS_ON=0 to 0.1*Vs $V_{\rm S}$ =13.5V, $R_{\rm L}$ =270 Ω	P_12.1.11
Turn OFF Rise time, PWM mode	t _{OFFR,PWM}	-	1	1.25	μs	$V_{\rm LS}$ 0.1*Vs to 0.9*Vs; $V_{\rm S}$ =13.5V, $R_{\rm L}$ =270Ω	P_12.1.12
Turn OFF Rise time, slow mode	t _{OFFR,Slow}	-	100	150	μs	²⁾ V_{LS} 0.1*Vs to 0.9*Vs; V_{S} =13.5V, R_{L} =270Ω	P_12.1.13
Minimum Duty Cycle Pulse Width variation	ton _{MIN}	1.5	2	3.5	μs	$ton(dig) = 2\mu s^{1)}$	P_12.1.14
Typical (systematic) Pulse Width increase LS_ON to VLS	d ton _{TYP}	-	1.25	-	μs	$ton(dig) = 2\mu s^{1)}$	P_12.1.15
Zener Clamp Voltage	V _{AZ}	-	50	-	V	values are valid at $T_{i} = 25^{\circ}C$	P_12.1.16
Clamping Energy (repetitive)	$E_{\rm clamp}$	-	-	2	mJ	¹⁾³⁾ 1.000.000 cycles, @ I _{max} = 90mA	P_12.1.17
Clamping Energy	E _{clamp}	-	-	14	mJ	¹⁾³⁾ 10 cycles, Tstart = P_12.1 25°C, @ I _{max} = 230mA	
Clamping Energy (single), hot	E _{clamp}	-	-	7	mJ	¹⁾³⁾ 10 cycles, Tstart = 85°C, @ I _{max} = 230mA	P_12.1.19



- 1) Not subject to production test, specified by design.
- 2) Static ON mode (no PWM)
- 3) valid for one low-side, not for both at the same time



Package Outlines

29 Package Outlines



Figure 41 Package outline VQFN-48-31 (with LTI)

Notes

- 1. You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products.
- 2. Dimensions in mm.



Revision History

30 Revision History

Revision Histo	ry
Page or Item	Subjects (major changes since previous revision)
Rev. 1.0, 2016-	05-06
	Initial revision

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Edition 2016-05-06 Published by Infineon Technologies AG 81726 Munich, Germany

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